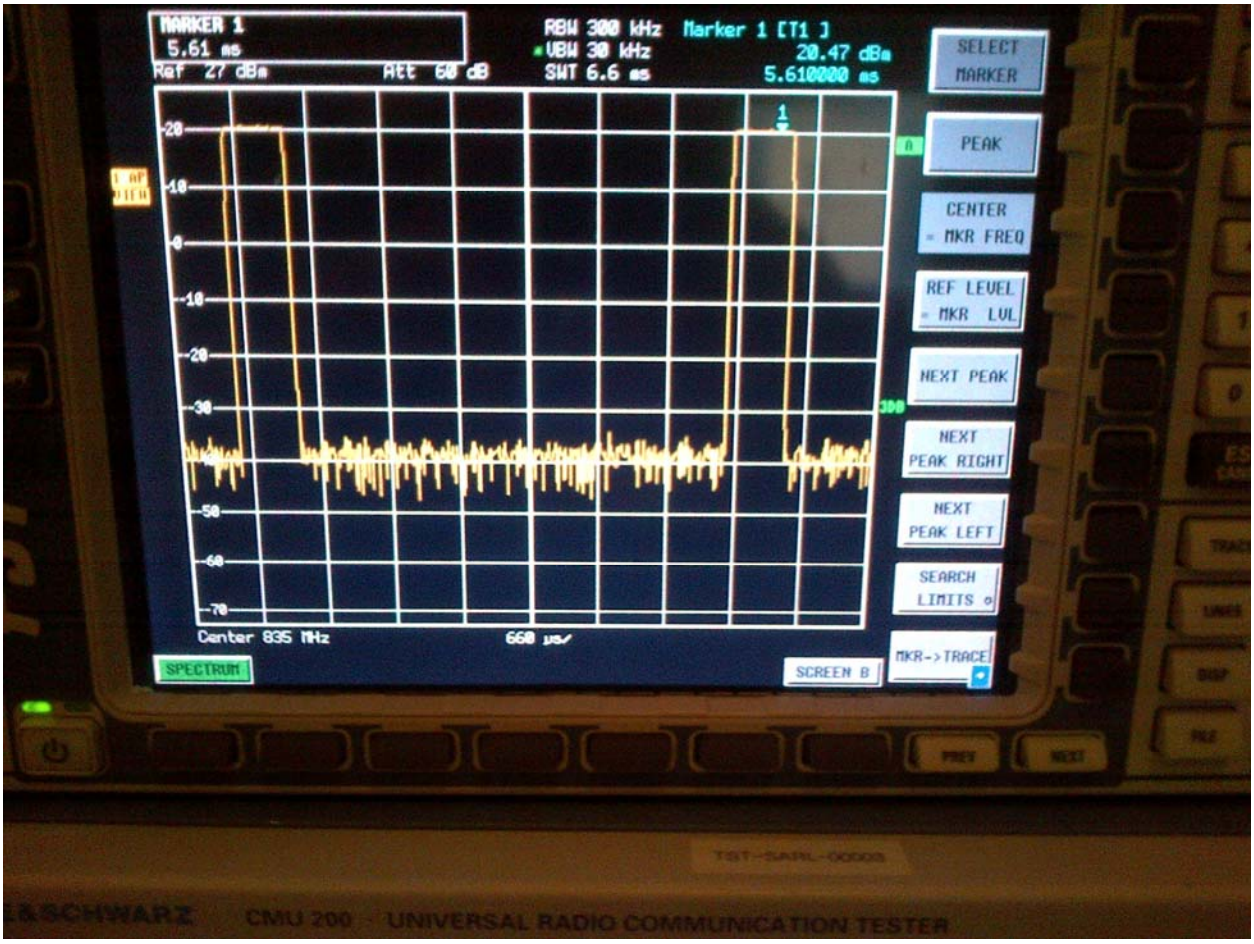
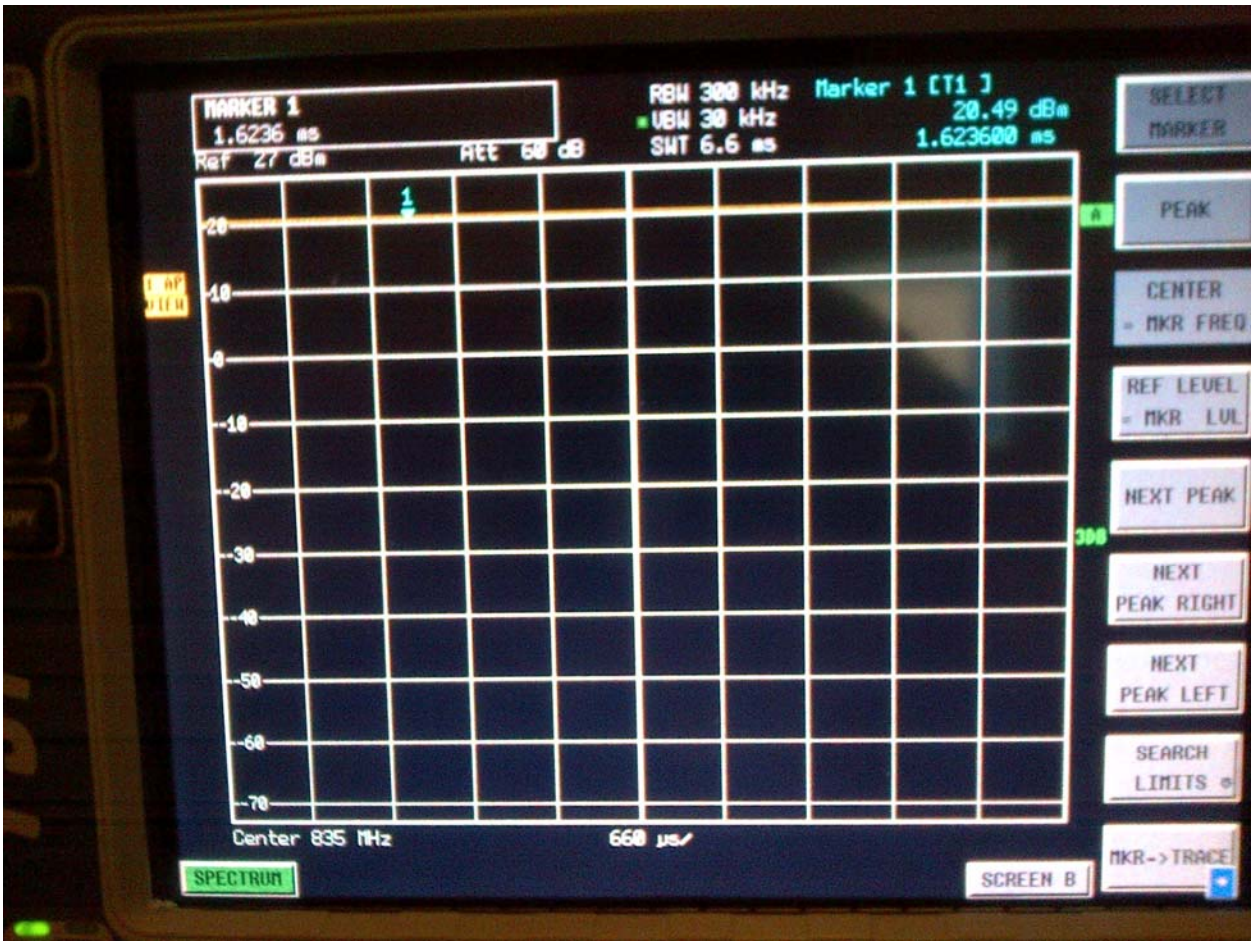
Annex A: Measurement data and plots

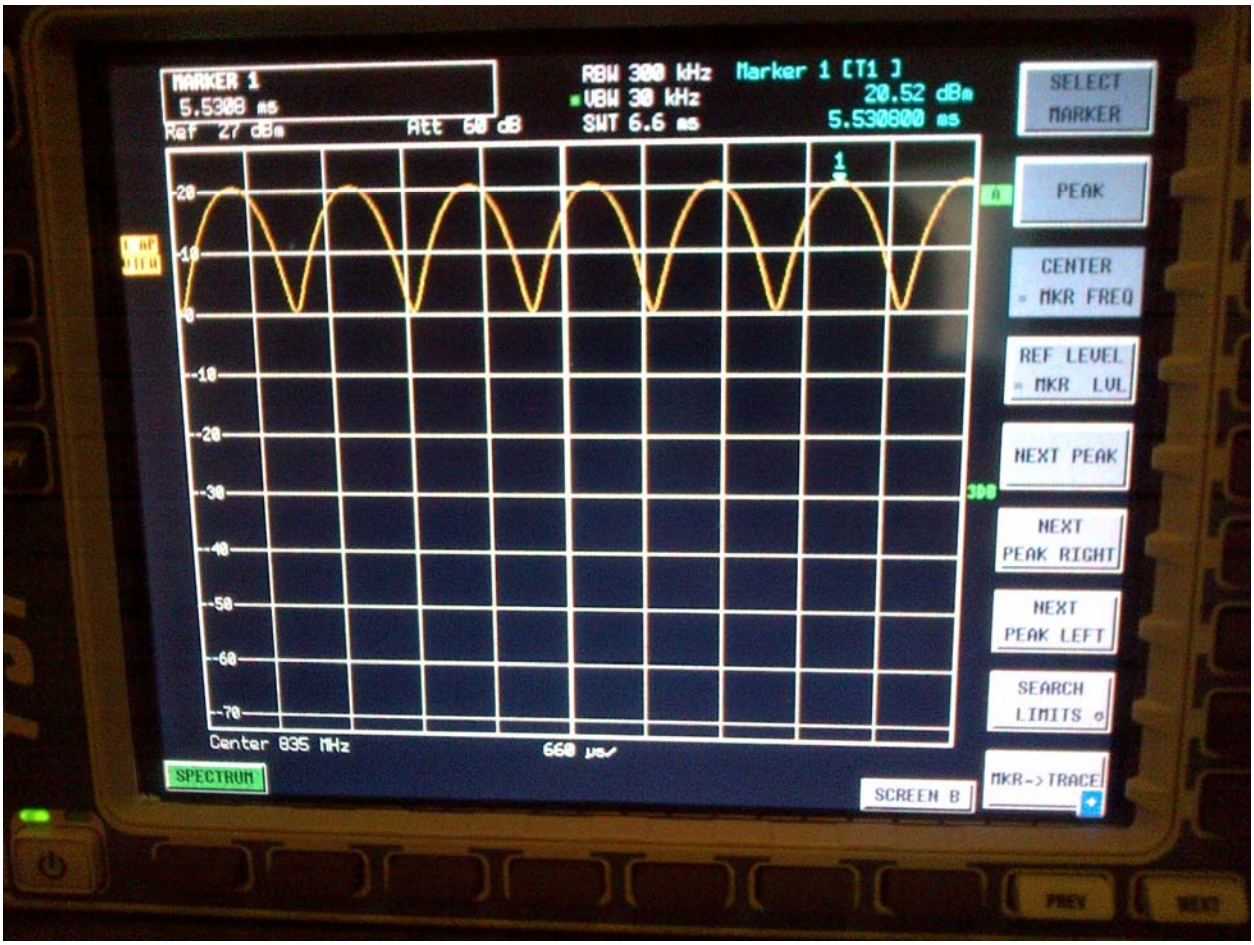
A.1 Spectrum analyser plots: GSM/UMTS, CW, 80%AM, signals



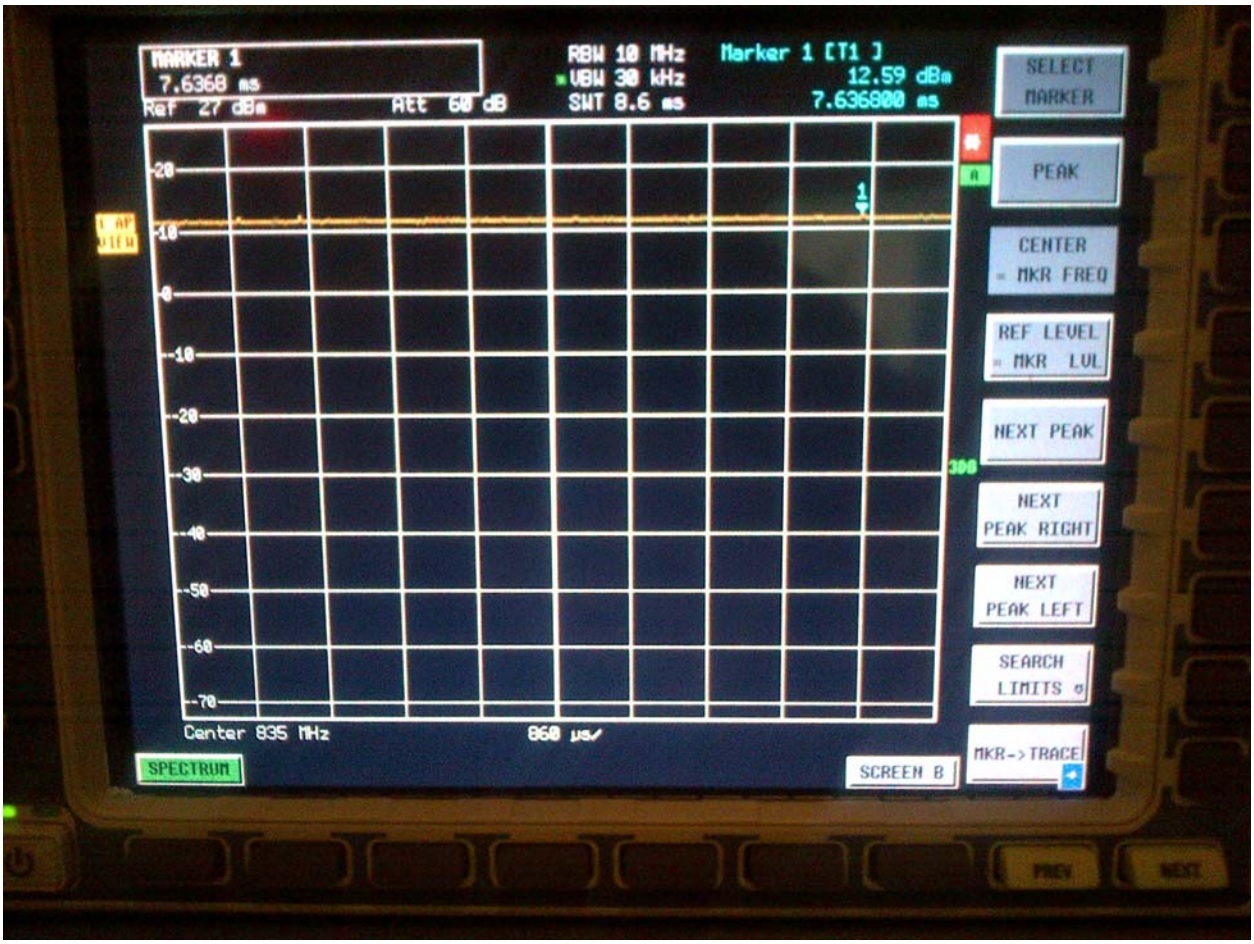
GSM 835 MHz



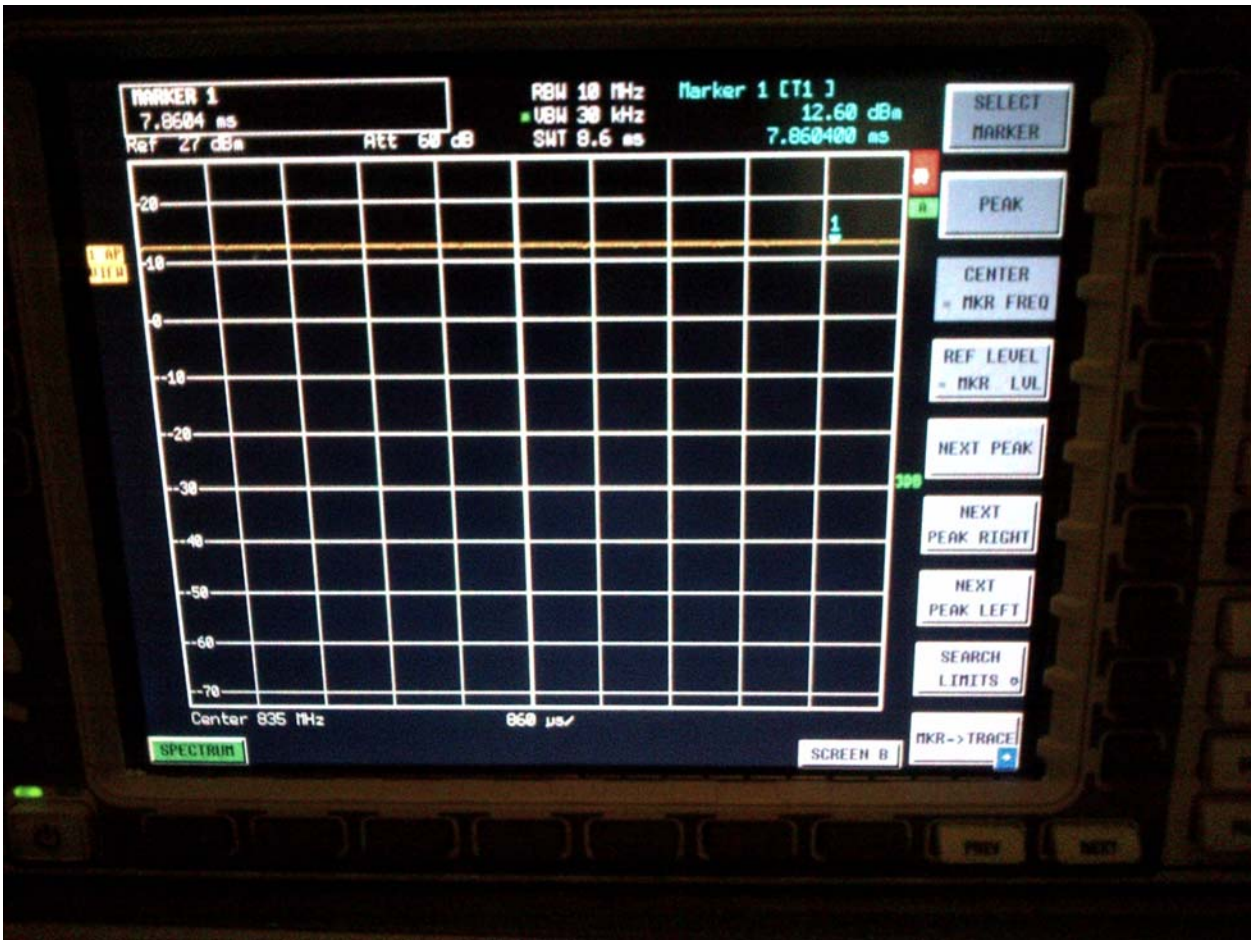
CW 835 MHz



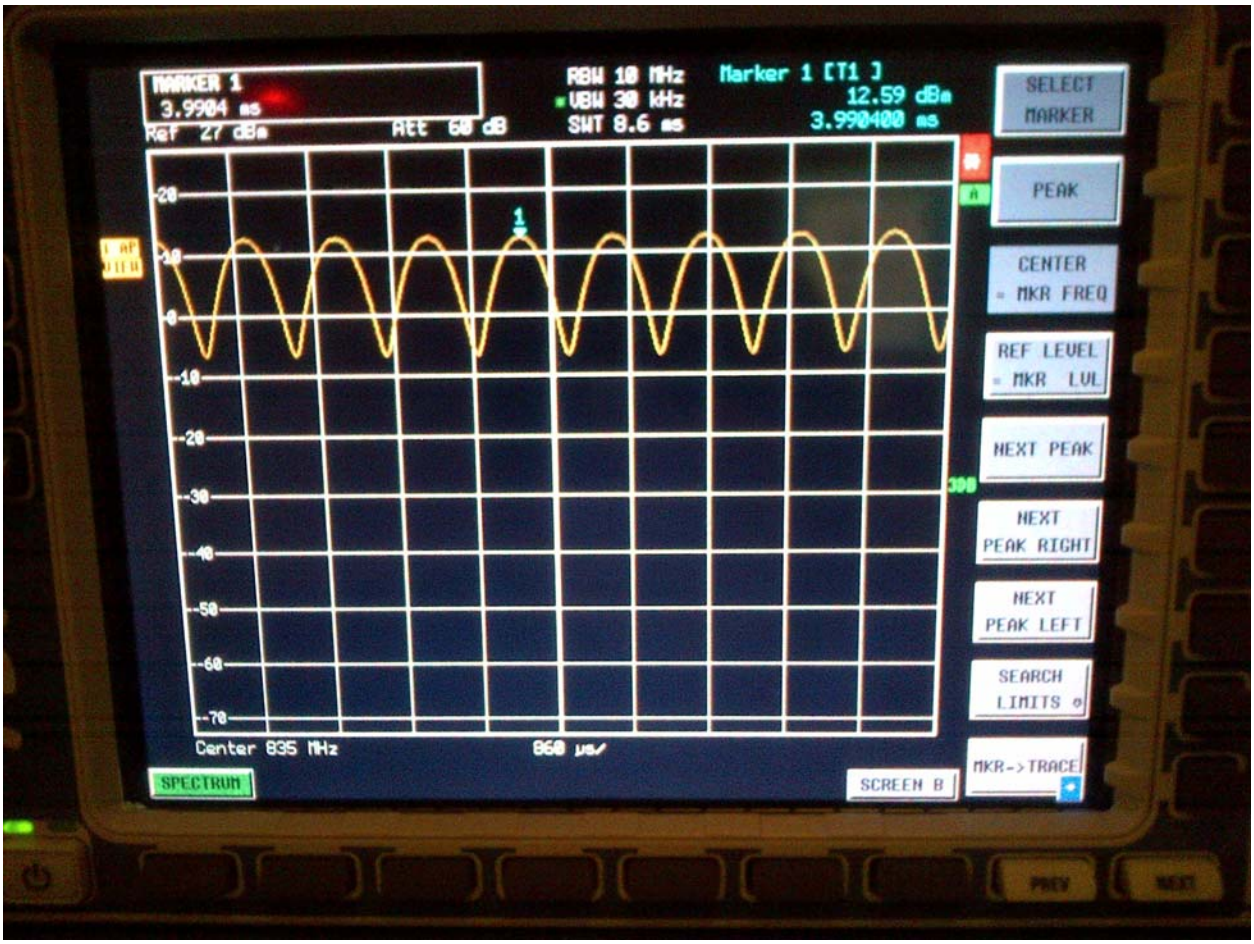
AM 80% 835 MHz



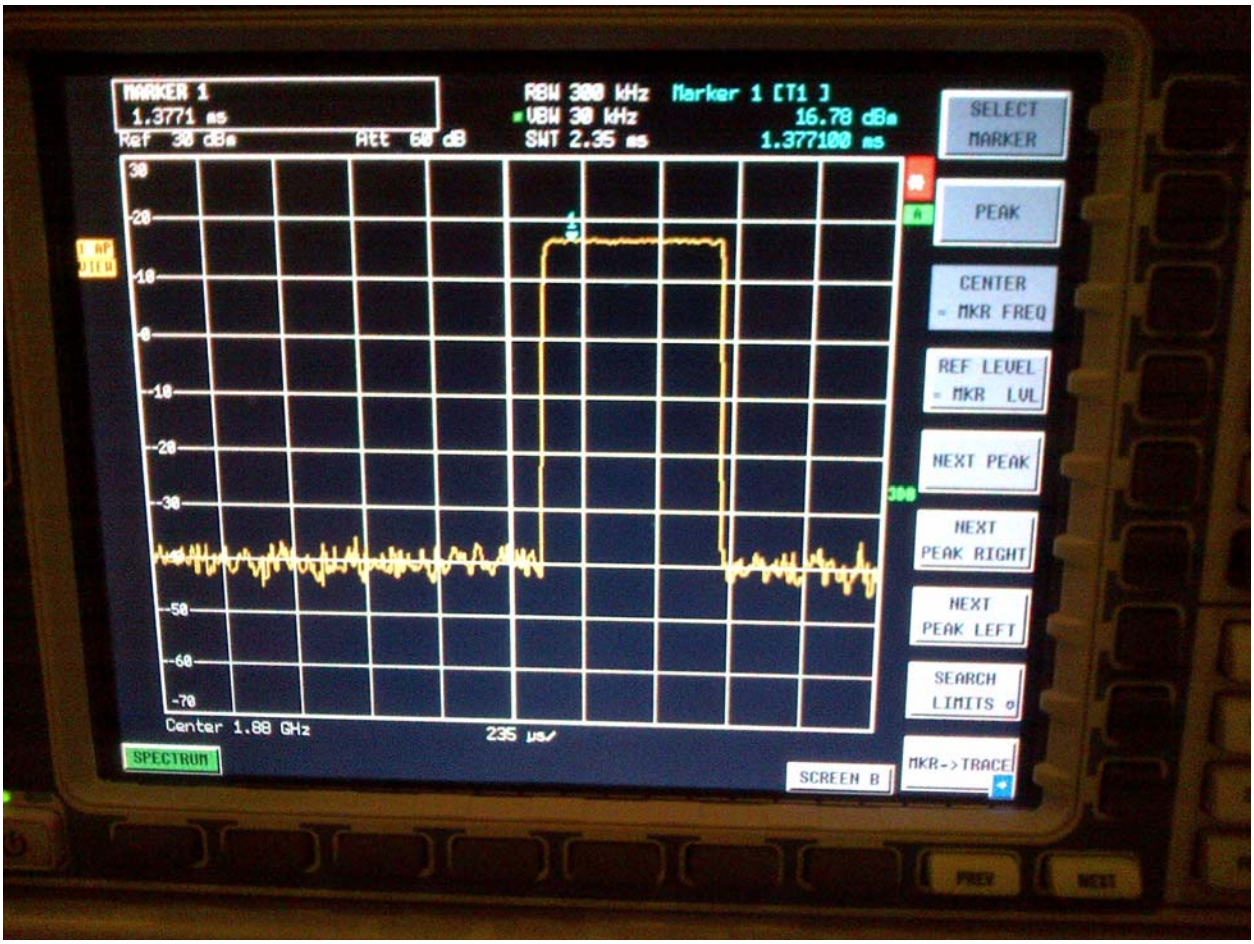
UMTS 835 MHz



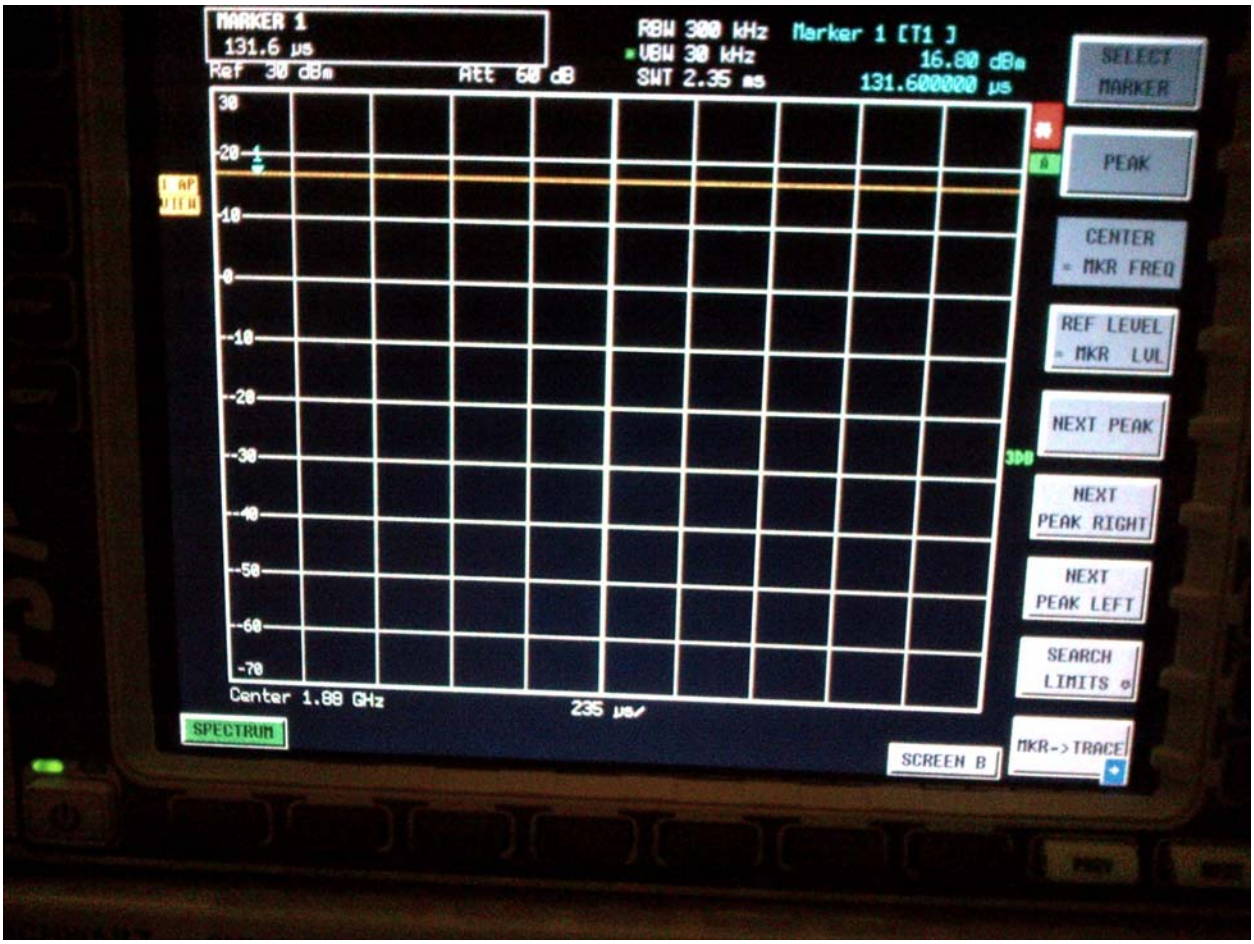
CW 835 MHz



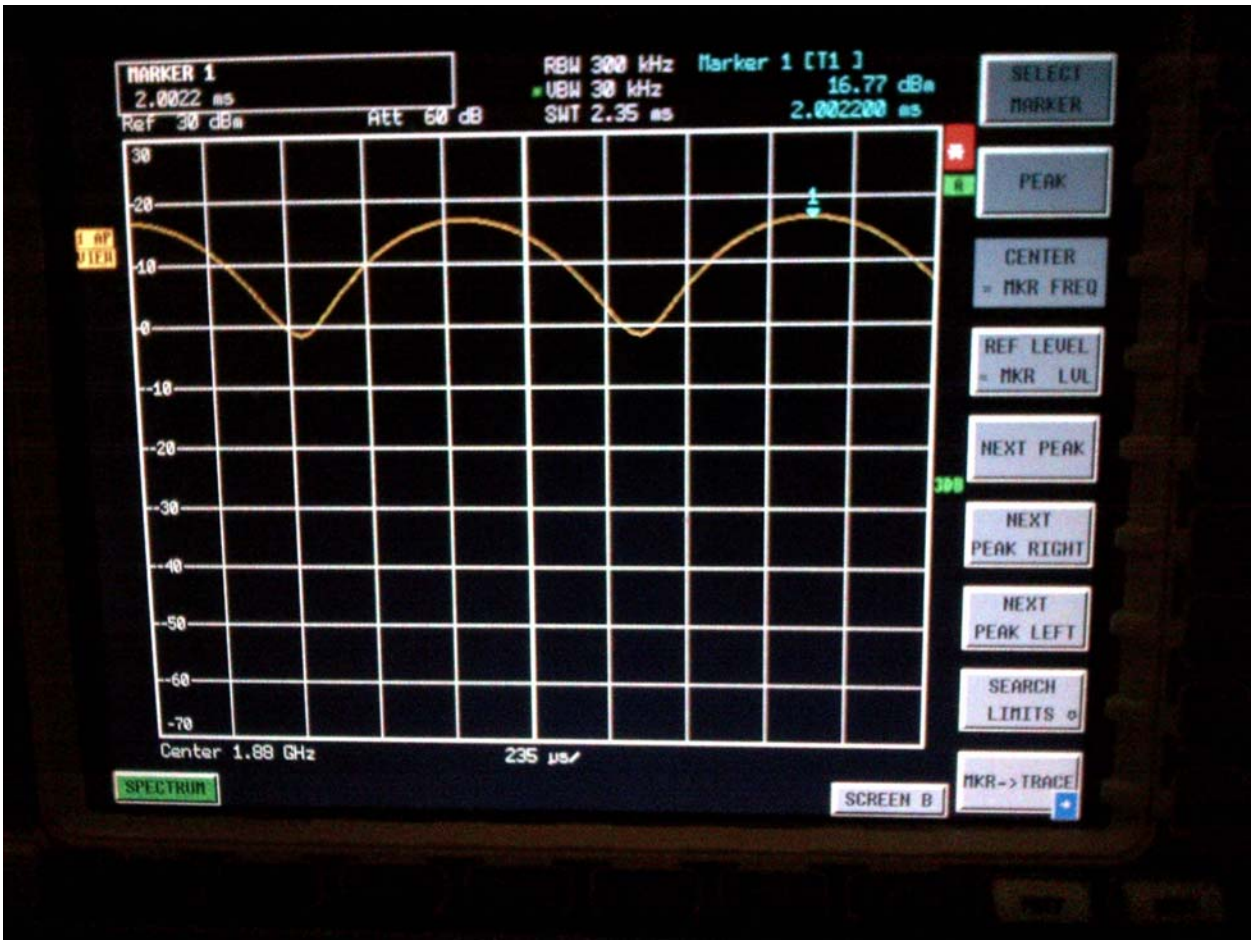
AM 80% 835 MHz



GSM 1880 MHz

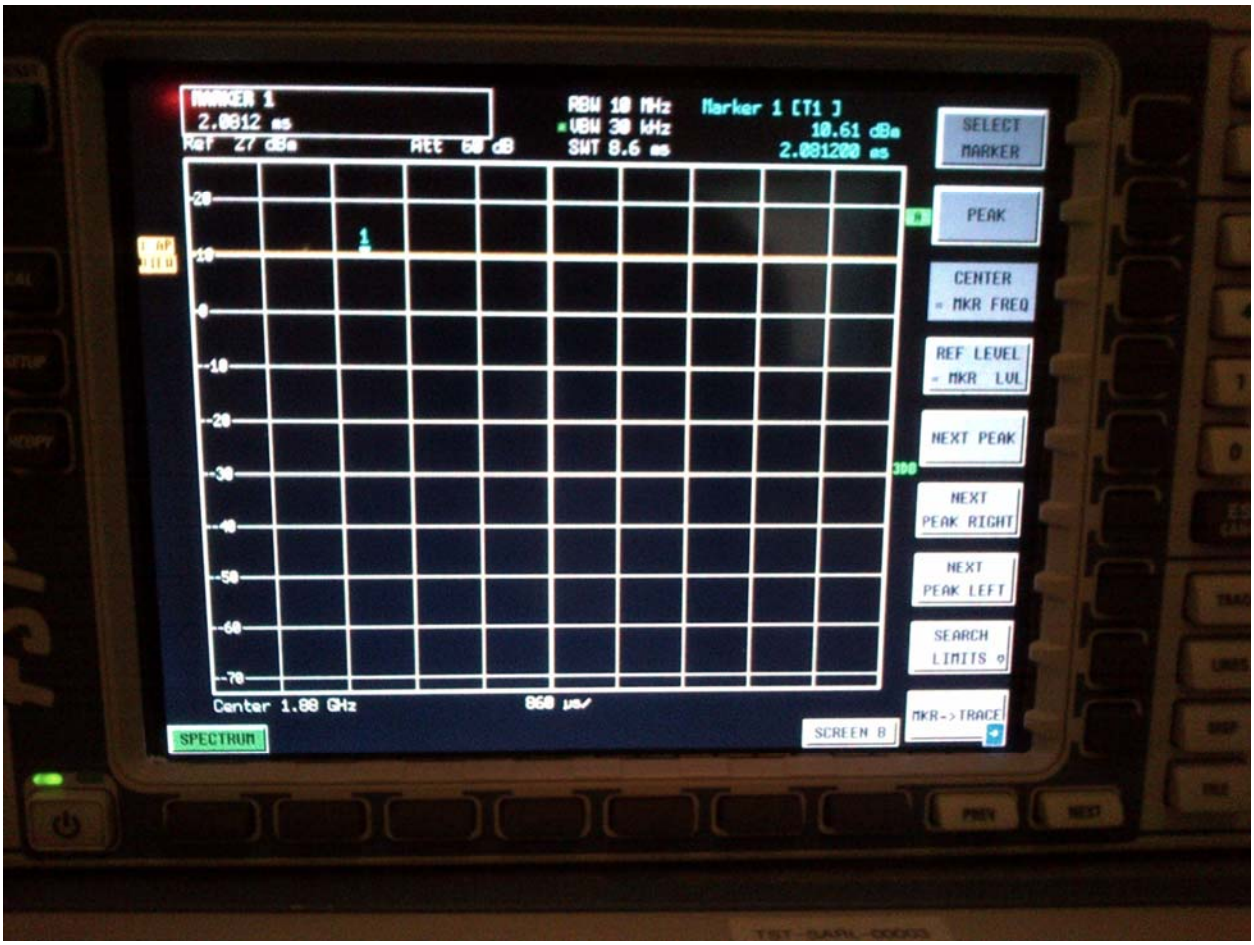


CW 1880 MHz

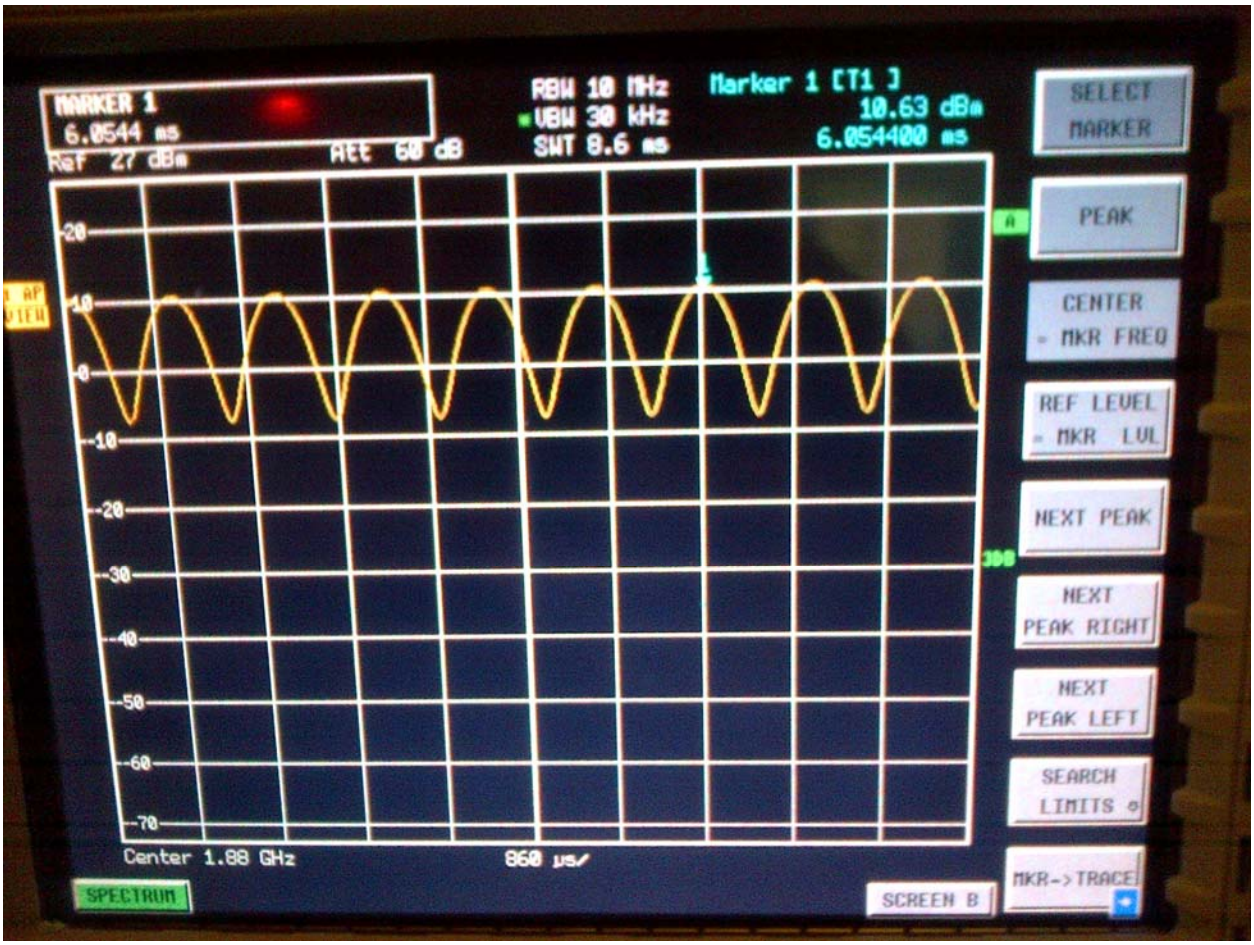


AM 80 % 1880 MHz

UMTS 1880 MHz



CW 1880 MHz



AM 80 % 1880 MHz

A.2 Dipole validation and probe modulation factor plots

Date/Time: 12/17/2012 11:31:29 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_validation_835 MHz_12_17_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: CW; Frequency: 835 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

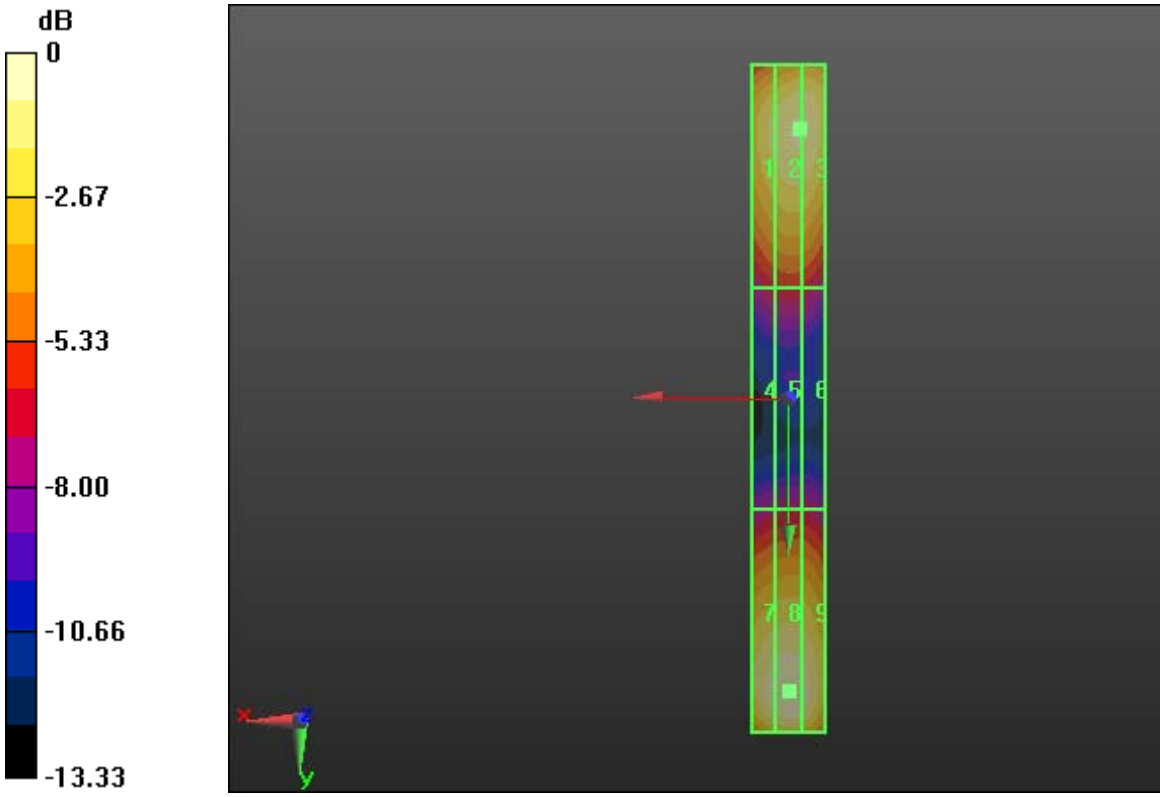
Dipole E-Field measurement/E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 106.6 V/m; Power Drift = -0.02 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 168.4 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **144.2 V/m**	Grid 2 **M4** **154.3 V/m**	Grid 3 **M4** **154.2 V/m**
Grid 4 **M4** **80.47 V/m**	Grid 5 **M4** **83.31 V/m**	Grid 6 **M4** **81.66 V/m**
Grid 7 **M4**	Grid 8 **M4**	Grid 9 **M4**

162.8 V/m	**168.4 V/m**	**161.7 V/m**

Cursor:
Total = 168.4 V/m
E Category: M4
Location: 0, 79, 4.7 mm



0 dB = 168.4V/m = 44.53 dB V/m

Date/Time: 6/28/2012 1:13:34 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_GSM835 MHz_06_28_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: GSM 835_PMF, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - GSM 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 34.76 V/m; Power Drift = -0.00 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 54.25 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **49.26 V/m**	Grid 2 **M4** **51.48 V/m**	Grid 3 **M4** **51.48 V/m**
Grid 4 **M4** **27.95 V/m**	Grid 5 **M4** **28.56 V/m**	Grid 6 **M4** **28.13 V/m**
Grid 7 **M4**	Grid 8 **M4**	Grid 9 **M4**

51.48 V/m	**54.25 V/m**	**53.95 V/m**

Cursor:
Total = 54.247 V/m
E Category: M4
Location: -2.5, 80.5, 4.7 mm

Dipole E-Field measurement/E Scan - CW 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 103.0 V/m; Power Drift = -0.02 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 162.8 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **148.5 V/m**	Grid 2 **M4** **160.5 V/m**	Grid 3 **M4** **160.4 V/m**
Grid 4 **M4** **82.74 V/m**	Grid 5 **M4** **86.24 V/m**	Grid 6 **M4** **84.62 V/m**
Grid 7 **M4** **158.1 V/m**	Grid 8 **M4** **162.8 V/m**	Grid 9 **M4** **155.2 V/m**

Cursor:
Total = 162.8 V/m
E Category: M4
Location: 0.5, 79.5, 4.7 mm

Dipole E-Field measurement/E Scan - AM80%_ 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

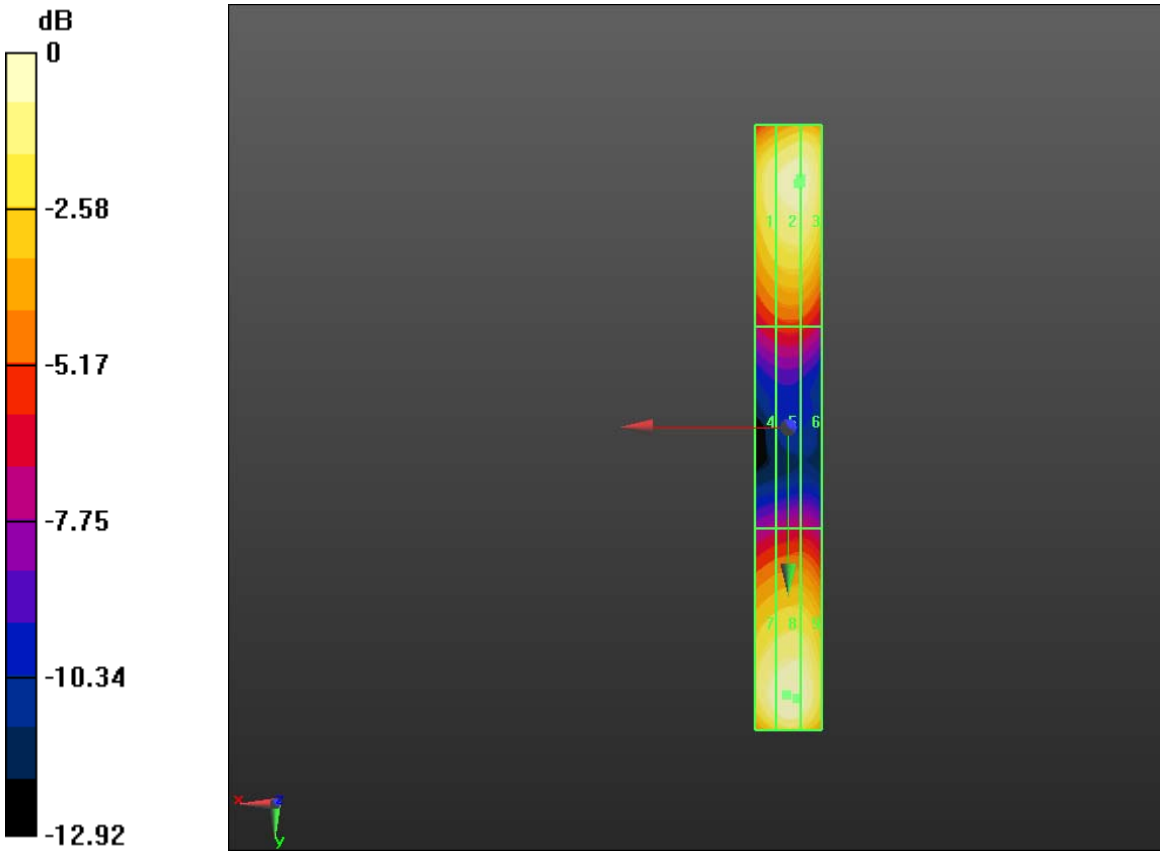
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 64.73 V/m; Power Drift = 0.02 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 102.0 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4**	Grid 2 **M4**	Grid 3 **M4**

93.30 V/m	**100.3 V/m**	**100.3 V/m**
Grid 4 **M4** **52.75 V/m**	Grid 5 **M4** **54.62 V/m**	Grid 6 **M4** **53.83 V/m**
Grid 7 **M4** **99.38 V/m**	Grid 8 **M4** **102.0 V/m**	Grid 9 **M4** **97.92 V/m**

Cursor:
Total = 102.0 V/m
E Category: M4
Location: 0.5, 79.5, 4.7 mm



0 dB = 54.250V/m = 34.69 dB V/m

Date/Time: 2/17/2012 12:24:15 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_UMTS835 MHz_02_17_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: WCDMA FDD V, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - UMTS 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 41.08 V/m; Power Drift = 0.03 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 64.41 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **53.11 V/m**	Grid 2 **M4** **55.59 V/m**	Grid 3 **M4** **55.40 V/m**
Grid 4 **M4** **29.72 V/m**	Grid 5 **M4** **30.66 V/m**	Grid 6 **M4** **29.79 V/m**
Grid 7 **M4** **61.55 V/m**	Grid 8 **M4** **64.41 V/m**	Grid 9 **M4** **63.22 V/m**

Cursor:
Total = 64.412 V/m
E Category: M4
Location: -0.5, 79, 4.7 mm

Dipole E-Field measurement/E Scan - CW 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 43.11 V/m; Power Drift = -0.14 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 68.64 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **58.55 V/m**	Grid 2 **M4** **59.20 V/m**	Grid 3 **M4** **57.13 V/m**
Grid 4 **M4** **32.35 V/m**	Grid 5 **M4** **32.63 V/m**	Grid 6 **M4** **31.24 V/m**
Grid 7 **M4** **61.85 V/m**	Grid 8 **M4** **68.64 V/m**	Grid 9 **M4** **68.56 V/m**

Cursor:
Total = 68.635 V/m
E Category: M4
Location: -3, 79.5, 4.7 mm

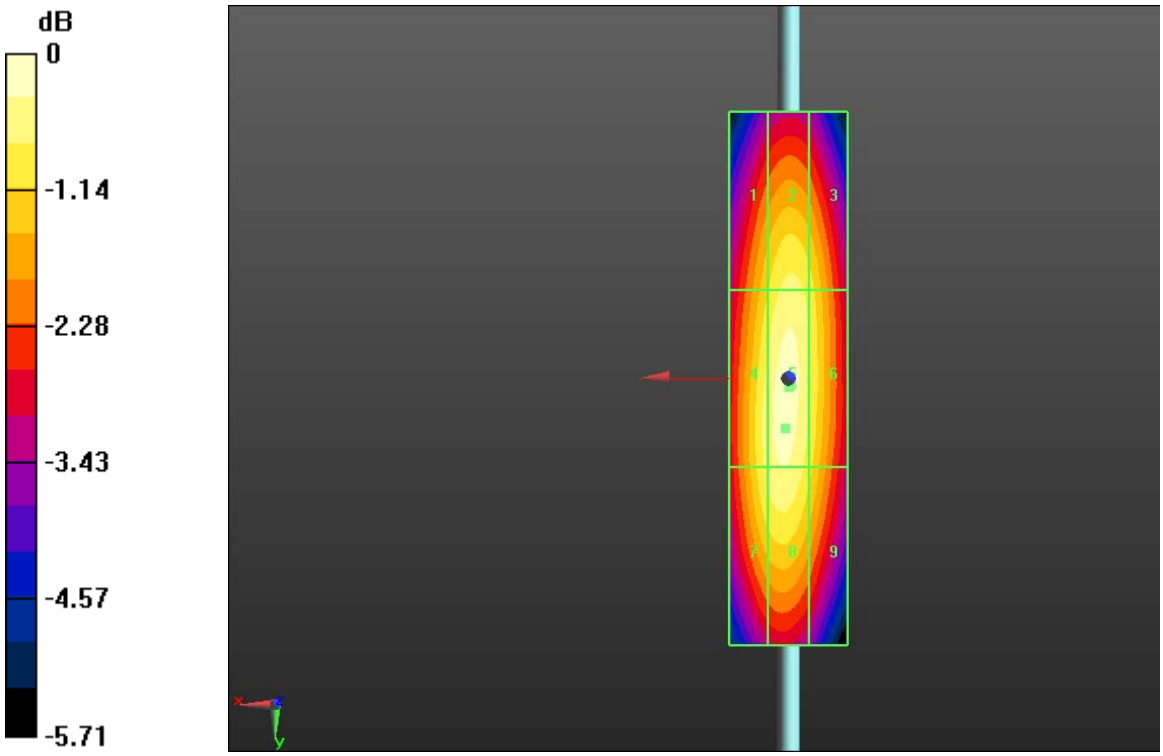
Dipole E-Field measurement/E Scan - AM80%_ 835_PMF/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 28.41 V/m; Power Drift = 0.09 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 45.21 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **38.28 V/m**	Grid 2 **M4** **38.73 V/m**	Grid 3 **M4** **37.25 V/m**
Grid 4 **M4** **21.72 V/m**	Grid 5 **M4** **21.89 V/m**	Grid 6 **M4** **20.80 V/m**
Grid 7 **M4** **40.90 V/m**	Grid 8 **M4** **45.21 V/m**	Grid 9 **M4** **45.16 V/m**

Cursor:
Total = 45.209 V/m
E Category: M4
Location: -3, 79.5, 4.7 mm



0 dB = 0.180A/m = -14.89 dB A/m

Date/Time: 12/17/2012 11:54:55 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_validation_1880 MHz_12_17_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CW; Frequency: 1880 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

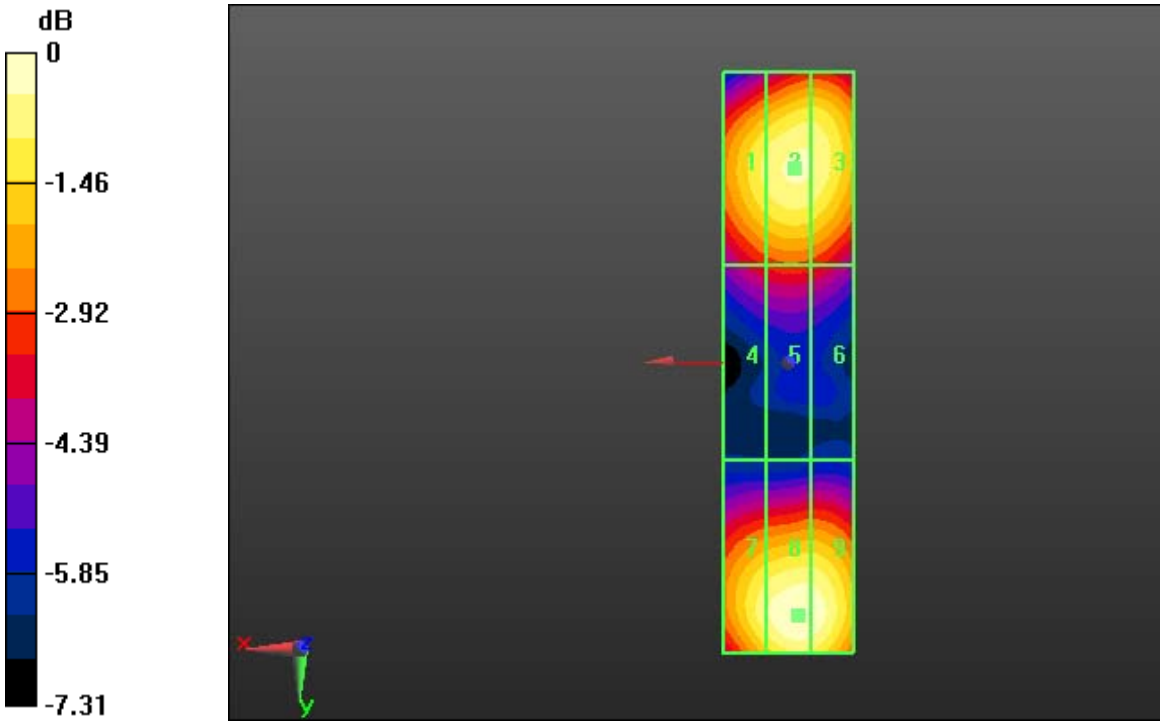
Dipole E-Field measurement/E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 145.2 V/m; Power Drift = -0.03 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 128.6 V/m
Near-field category: M2 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M2** **117.2 V/m**	Grid 2 **M2** **123.0 V/m**	Grid 3 **M2** **122.0 V/m**
Grid 4 **M3** **87.82 V/m**	Grid 5 **M3** **90.83 V/m**	Grid 6 **M3** **89.07 V/m**
Grid 7 **M2**	Grid 8 **M2**	Grid 9 **M2**

120.5 V/m	**128.6 V/m**	**127.6 V/m**

Cursor:
Total = 128.6 V/m
E Category: M2
Location: -1.5, 39, 4.7 mm



0 dB = 128.6V/m = 42.18 dB V/m

Date/Time: 6/28/2012 12:54:33 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_GSM1880 MHz_06_28_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: GSM 1880, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - GSM 1880_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 33.26 V/m; Power Drift = 0.00 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 29.81 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **27.34 V/m**	Grid 2 **M4** **28.65 V/m**	Grid 3 **M4** **28.59 V/m**
Grid 4 **M4** **19.83 V/m**	Grid 5 **M4** **20.51 V/m**	Grid 6 **M4** **20.10 V/m**
Grid 7 **M4**	Grid 8 **M4**	Grid 9 **M4**

28.20 V/m	**29.81 V/m**	**29.37 V/m**

Cursor:
Total = 29.810 V/m
E Category: M4
Location: -1, 38.5, 4.7 mm

Dipole E-Field measurement/E Scan- CW 1800_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 95.34 V/m; Power Drift = 0.01 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 84.88 V/m
Near-field category: M3 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M3** **78.80 V/m**	Grid 2 **M3** **82.95 V/m**	Grid 3 **M3** **82.43 V/m**
Grid 4 **M4** **56.84 V/m**	Grid 5 **M4** **58.53 V/m**	Grid 6 **M4** **56.53 V/m**
Grid 7 **M3** **80.11 V/m**	Grid 8 **M3** **84.88 V/m**	Grid 9 **M3** **83.31 V/m**

Cursor:
Total = 84.885 V/m
E Category: M3
Location: -0.5, 38.5, 4.7 mm

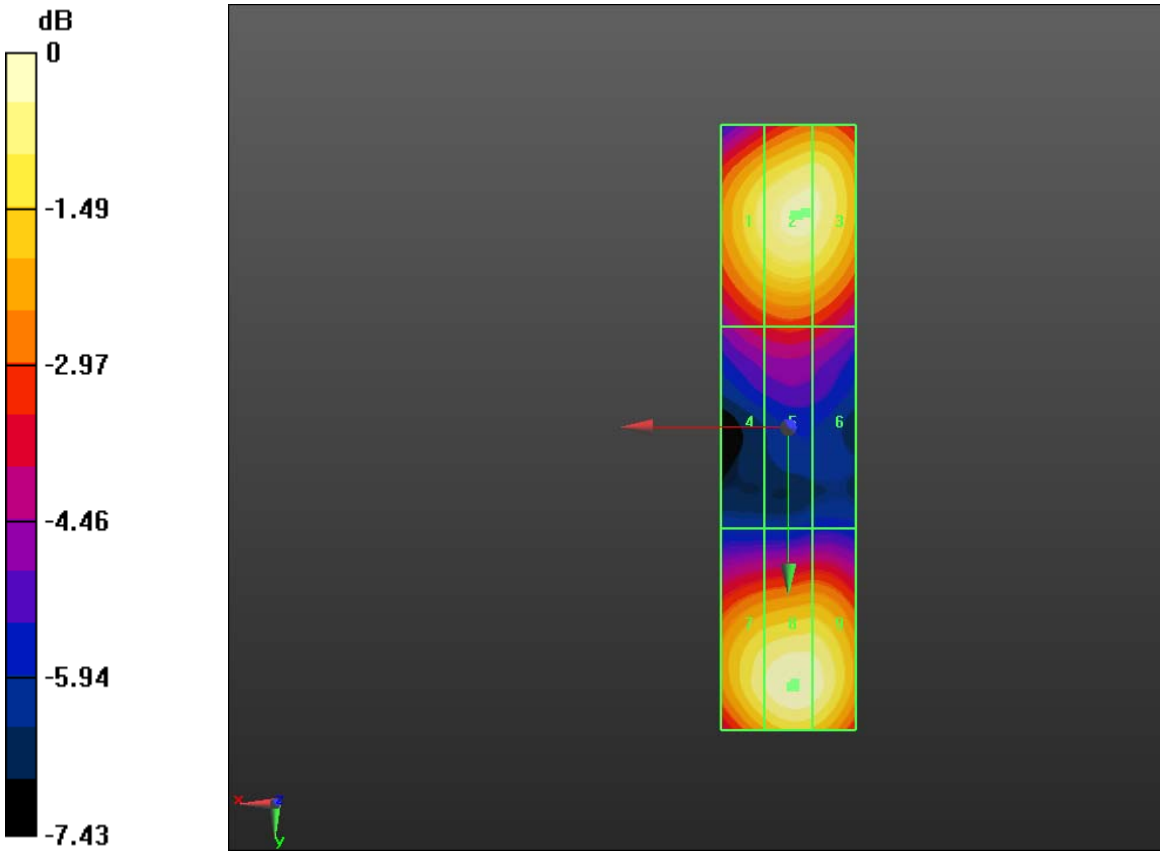
Dipole E-Field measurement/E Scan - AM80%_ 1880_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 60.62 V/m; Power Drift = -0.03 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 53.60 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **49.75 V/m**	Grid 2 **M4** **52.55 V/m**	Grid 3 **M4** **52.06 V/m**
Grid 4 **M4** **35.78 V/m**	Grid 5 **M4** **36.92 V/m**	Grid 6 **M4** **36.02 V/m**
Grid 7 **M4** **50.66 V/m**	Grid 8 **M4** **53.60 V/m**	Grid 9 **M4** **52.63 V/m**

Cursor:
Total = 53.599 V/m
E Category: M4
Location: -1, 38, 4.7 mm



0 dB = 29.810V/m = 29.49 dB V/m

Date/Time: 2/17/2012 2:20:23 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_PMF_UMTS1880 MHz_02_17_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: WCDMA FDD II, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole E-Field measurement/E Scan - UMTS 1880_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 47.02 V/m; Power Drift = 0.01 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 42.43 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **37.98 V/m**	Grid 2 **M4** **39.42 V/m**	Grid 3 **M4** **39.04 V/m**
Grid 4 **M4** **26.86 V/m**	Grid 5 **M4** **27.50 V/m**	Grid 6 **M4** **26.70 V/m**
Grid 7 **M4** **39.63 V/m**	Grid 8 **M4** **42.43 V/m**	Grid 9 **M4** **41.87 V/m**

Cursor:
Total = 42.427 V/m
E Category: M4
Location: -1, 38, 4.7 mm

Dipole E-Field measurement/E Scan- CW 1800_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 47.33 V/m; Power Drift = -0.05 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 42.41 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **38.23 V/m**	Grid 2 **M4** **39.51 V/m**	Grid 3 **M4** **39.41 V/m**
Grid 4 **M4** **26.94 V/m**	Grid 5 **M4** **27.41 V/m**	Grid 6 **M4** **26.77 V/m**
Grid 7 **M4** **40.02 V/m**	Grid 8 **M4** **42.41 V/m**	Grid 9 **M4** **41.99 V/m**

Cursor:
Total = 42.409 V/m
E Category: M4
Location: -1.5, 38, 4.7 mm

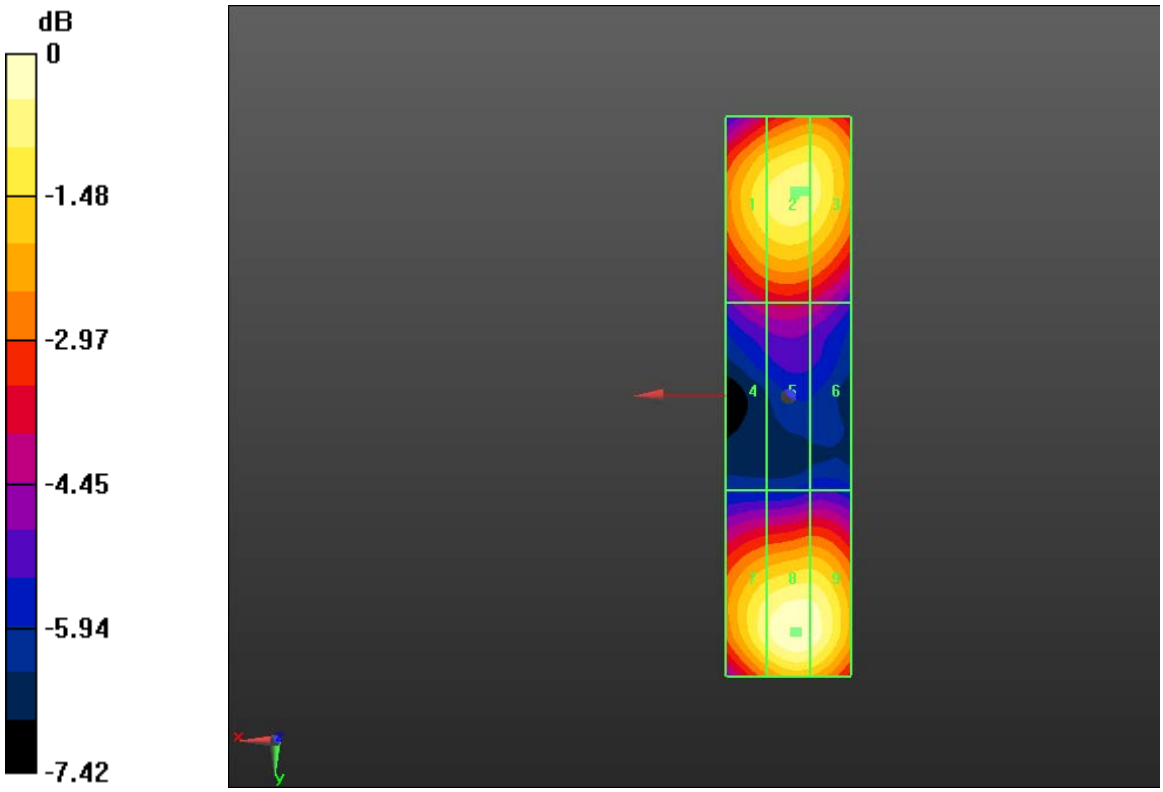
Dipole E-Field measurement/E Scan - AM80%_ 1880_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 30.18 V/m; Power Drift = 0.06 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 27.40 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **24.40 V/m**	Grid 2 **M4** **25.26 V/m**	Grid 3 **M4** **24.95 V/m**
Grid 4 **M4** **17.20 V/m**	Grid 5 **M4** **17.65 V/m**	Grid 6 **M4** **17.12 V/m**
Grid 7 **M4** **25.54 V/m**	Grid 8 **M4** **27.40 V/m**	Grid 9 **M4** **27.02 V/m**

Cursor:
Total = 27.402 V/m
E Category: M4
Location: -1, 38, 4.7 mm



0 dB = 42.430V/m = 32.55 dB V/m

Date/Time: 12/18/2012 12:59:09 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_validation_835 MHz_12_18_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: CW; Frequency: 835 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

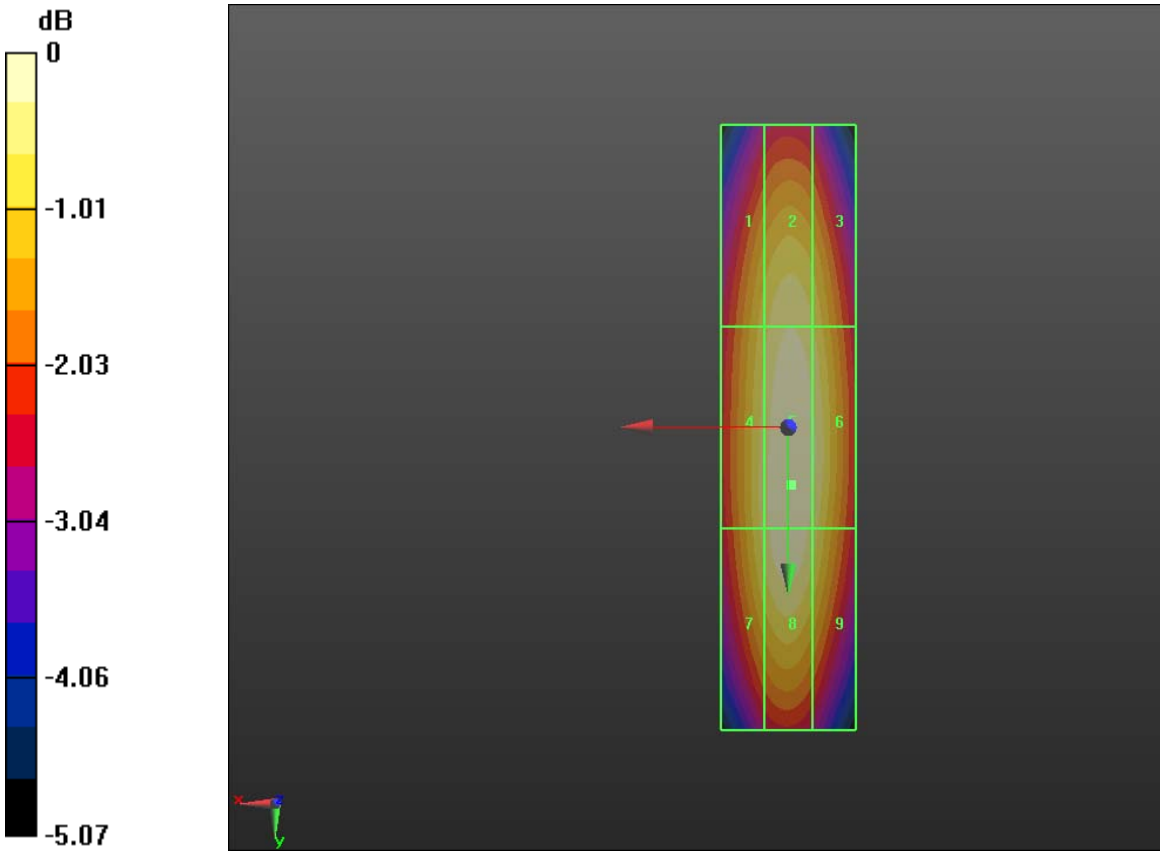
Dipole H-Field measurement with H3DV6 probe/H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.47 V/m; Power Drift = 0.10 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.44 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.40 A/m**	Grid 2 **M4** **0.42 A/m**	Grid 3 **M4** **0.41 A/m**
Grid 4 **M4** **0.42 A/m**	Grid 5 **M4** **0.44 A/m**	Grid 6 **M4** **0.43 A/m**
Grid 7 **M4**	Grid 8 **M4**	Grid 9 **M4**

0.42 A/m	**0.44 A/m**	**0.42 A/m**

Cursor:
Total = 0.444 A/m
H Category: M4
Location: -0.5, 8.5, 4.7 mm



0 dB = 0.440A/m = -7.13 dB A/m

Date/Time: 6/28/2012 11:48:13 AM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_GSM835 MHz_06_28_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: GSM 835_PMF, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - GSM 835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.17 V/m; Power Drift = -0.01 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.16 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.15 A/m**	Grid 2 **M4** **0.16 A/m**	Grid 3 **M4** **0.15 A/m**
Grid 4 **M4**	Grid 5 **M4**	Grid 6 **M4**

0.16 A/m	**0.16 A/m**	**0.16 A/m**
Grid 7 **M4** **0.15 A/m**	Grid 8 **M4** **0.16 A/m**	Grid 9 **M4** **0.15 A/m**

Cursor:
Total = 0.163 A/m
H Category: M4
Location: 0, 8.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW 835_PMF/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.28 V/m; Power Drift = 0.08 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.47 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.44 A/m**	Grid 2 **M4** **0.46 A/m**	Grid 3 **M4** **0.44 A/m**
Grid 4 **M4** **0.45 A/m**	Grid 5 **M4** **0.47 A/m**	Grid 6 **M4** **0.45 A/m**
Grid 7 **M4** **0.45 A/m**	Grid 8 **M4** **0.47 A/m**	Grid 9 **M4** **0.44 A/m**

Cursor:
Total = 0.471 A/m
H Category: M4
Location: 0, 8, 4.7 mm

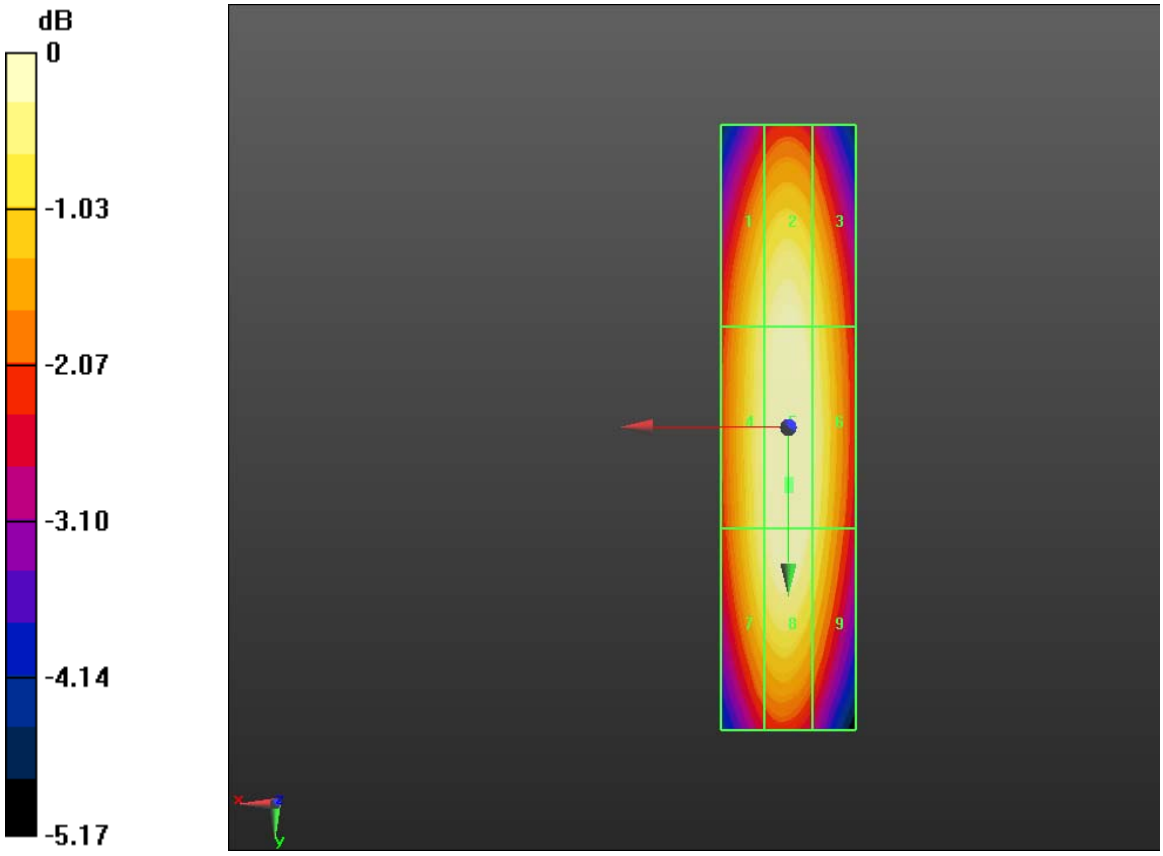
Dipole H-Field measurement with H3DV6 probe/H Scan - AM80%_PMF/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.32 V/m; Power Drift = 0.12 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.30 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.28 A/m**	Grid 2 **M4** **0.29 A/m**	Grid 3 **M4** **0.28 A/m**
Grid 4 **M4** **0.29 A/m**	Grid 5 **M4** **0.30 A/m**	Grid 6 **M4** **0.29 A/m**
Grid 7 **M4** **0.29 A/m**	Grid 8 **M4** **0.30 A/m**	Grid 9 **M4** **0.28 A/m**

Cursor:
Total = 0.304 A/m
H Category: M4
Location: 0, 9, 4.7 mm



0 dB = 0.160A/m = -15.92 dB A/m

Date/Time: 2/17/2012 4:08:25 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_UMTS835 MHz_02_17_12

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1011

Communication System: WCDMA FDD V, Communication System: CW, Communication System: AM 80%; Frequency: 835 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan - UMTS 835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.19 V/m; Power Drift = 0.05 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.18 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.16 A/m**	Grid 2 **M4** **0.17 A/m**	Grid 3 **M4** **0.16 A/m**
Grid 4 **M4** **0.17 A/m**	Grid 5 **M4** **0.18 A/m**	Grid 6 **M4** **0.17 A/m**
Grid 7 **M4** **0.17 A/m**	Grid 8 **M4** **0.18 A/m**	Grid 9 **M4** **0.17 A/m**

Cursor:
Total = 0.181 A/m
H Category: M4
Location: 0.5, 8.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW 835_PMF/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.11 V/m; Power Drift = 0.08 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.20 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.17 A/m**	Grid 2 **M4** **0.19 A/m**	Grid 3 **M4** **0.18 A/m**
Grid 4 **M4** **0.18 A/m**	Grid 5 **M4** **0.20 A/m**	Grid 6 **M4** **0.19 A/m**
Grid 7 **M4** **0.18 A/m**	Grid 8 **M4** **0.19 A/m**	Grid 9 **M4** **0.18 A/m**

Cursor:
Total = 0.197 A/m
H Category: M4
Location: -0.5, 1, 4.7 mm

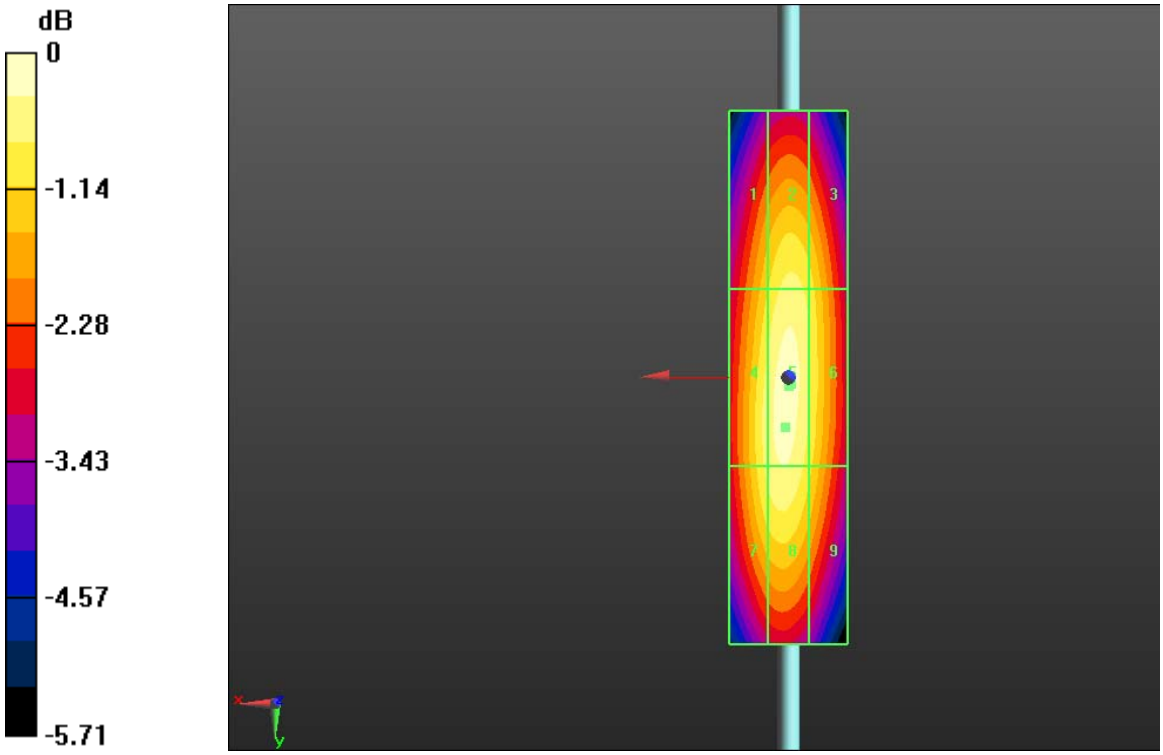
Dipole H-Field measurement with H3DV6 probe/H Scan - AM80%_PMF/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.14 V/m; Power Drift = 0.10 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.13 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.11 A/m**	Grid 2 **M4** **0.12 A/m**	Grid 3 **M4** **0.12 A/m**
Grid 4 **M4** **0.12 A/m**	Grid 5 **M4** **0.13 A/m**	Grid 6 **M4** **0.12 A/m**
Grid 7 **M4** **0.12 A/m**	Grid 8 **M4** **0.12 A/m**	Grid 9 **M4** **0.12 A/m**

Cursor:
Total = 0.127 A/m
H Category: M4
Location: 0, 1.5, 4.7 mm



0 dB = 0.180A/m = -14.89 dB A/m

Date/Time: 12/18/2012 1:06:37 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_validation_1880 MHz_12_18_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: CW; Frequency: 1880 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA;
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

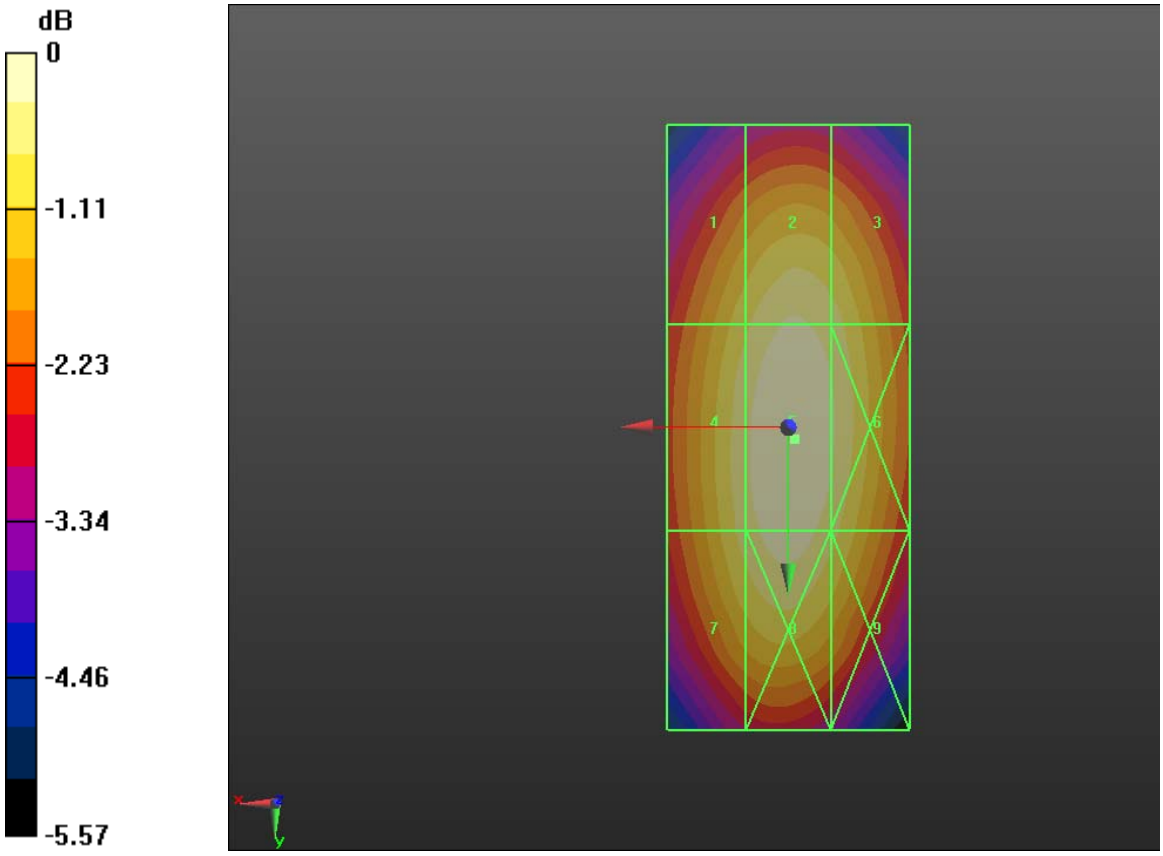
Dipole H-Field measurement with H3DV6 probe/H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.47 V/m; Power Drift = -0.04 dB
PMF = 1.00 is applied.
H-field emissions = 0.446 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.411 A/m**	Grid 2 **M4** **0.429 A/m**	Grid 3 **M4** **0.420 A/m**
Grid 4 **M4** **0.429 A/m**	Grid 5 **M4** **0.446 A/m**	Grid 6 **M4** **0.429 A/m**
Grid 7 **M4**	Grid 8 **M4**	Grid 9 **M4**

0.420 A/m	**0.438 A/m**	**0.420 A/m**

Cursor:
Total = 0.446 A/m
H Category: M4
Location: -0.5, 1, 4.7 mm



0 dB = 0.446A/m = -7.01 dB A/m

Date/Time: 6/28/2012 12:25:06 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_GSM1880 MHz_06_28_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: GSM 1880_PMF, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan -GSM 1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.11 V/m; Power Drift = -0.01 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.11 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.10 A/m**	Grid 2 **M4** **0.10 A/m**	Grid 3 **M4** **0.10 A/m**
Grid 4 **M4**	Grid 5 **M4**	Grid 6 **M4**

0.10 A/m	**0.11 A/m**	**0.10 A/m**
Grid 7 **M4** **0.10 A/m**	Grid 8 **M4** **0.10 A/m**	Grid 9 **M4** **0.10 A/m**

Cursor:
Total = 0.105 A/m
H Category: M4
Location: 0, 0.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW 1800_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement

grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.32 V/m; Power Drift = 0.00 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.30 A/m
Near-field category: M3 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M3** **0.28 A/m**	Grid 2 **M3** **0.29 A/m**	Grid 3 **M3** **0.28 A/m**
Grid 4 **M3** **0.29 A/m**	Grid 5 **M3** **0.30 A/m**	Grid 6 **M3** **0.29 A/m**
Grid 7 **M3** **0.28 A/m**	Grid 8 **M3** **0.29 A/m**	Grid 9 **M3** **0.28 A/m**

Cursor:
Total = 0.300 A/m
H Category: M3
Location: 0, 1, 4.7 mm

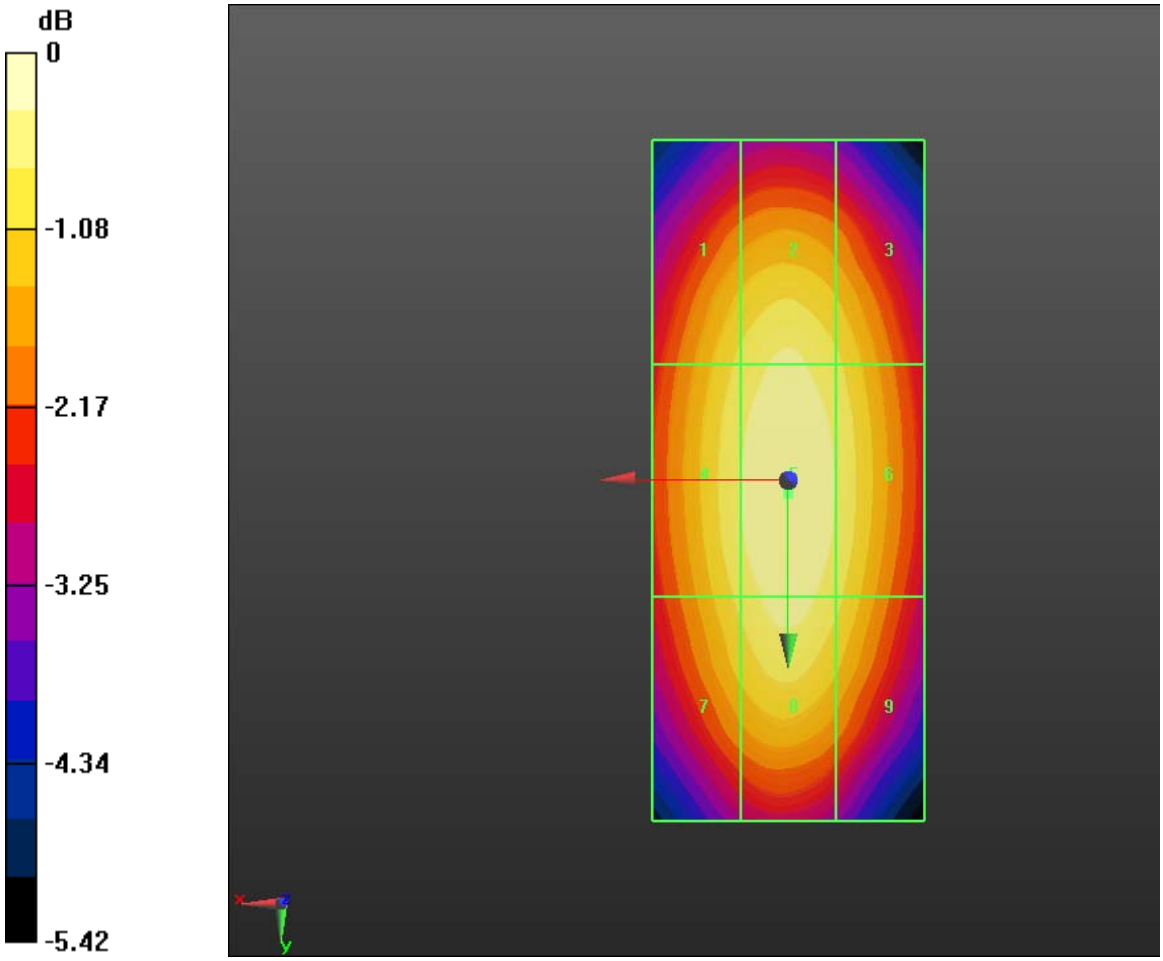
Dipole H-Field measurement with H3DV6 probe/H Scan - AM80%_1880_PMF/Hearing Aid Compatibility Test (41x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.21 V/m; Power Drift = 0.02 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.19 A/m
Near-field category: M3 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.18 A/m**	Grid 2 **M4** **0.19 A/m**	Grid 3 **M4** **0.18 A/m**
Grid 4 **M4** **0.19 A/m**	Grid 5 **M3** **0.19 A/m**	Grid 6 **M4** **0.19 A/m**
Grid 7 **M4** **0.18 A/m**	Grid 8 **M3** **0.19 A/m**	Grid 9 **M4** **0.18 A/m**

Cursor:
Total = 0.194 A/m
H Category: M3
Location: 0, 0.5, 4.7 mm



0 dB = 0.110A/m = -19.17 dB A/m

Date/Time: 2/17/2012 3:56:44 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_PMF_UMTS1880 MHz_02_17_12

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1008

Communication System: WCDMA FDD II, Communication System: CW, Communication System: AM 80%; Frequency: 1880 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/8/2011
- Sensor-Surface: (Fix Surface), z = 4.7
- Electronics: DAE3 Sn472; Calibrated: 3/7/2011
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Dipole H-Field measurement with H3DV6 probe/H Scan -UMTS 1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.16 V/m; Power Drift = 0.06 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.15 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.14 A/m**	Grid 2 **M4** **0.14 A/m**	Grid 3 **M4** **0.14 A/m**
Grid 4 **M4** **0.14 A/m**	Grid 5 **M4** **0.15 A/m**	Grid 6 **M4** **0.14 A/m**
Grid 7 **M4** **0.14 A/m**	Grid 8 **M4** **0.15 A/m**	Grid 9 **M4** **0.14 A/m**

Cursor:
Total = 0.150 A/m
H Category: M4
Location: 0, 0.5, 4.7 mm

Dipole H-Field measurement with H3DV6 probe/H Scan - CW 1880_PMF/Hearing Aid Compatibility Test (41x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.16 V/m; Power Drift = -0.01 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.15 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.14 A/m**	Grid 2 **M4** **0.14 A/m**	Grid 3 **M4** **0.14 A/m**
Grid 4 **M4** **0.14 A/m**	Grid 5 **M4** **0.15 A/m**	Grid 6 **M4** **0.14 A/m**
Grid 7 **M4** **0.14 A/m**	Grid 8 **M4** **0.15 A/m**	Grid 9 **M4** **0.14 A/m**

Cursor:
Total = 0.149 A/m
H Category: M4
Location: 0, 0.5, 4.7 mm

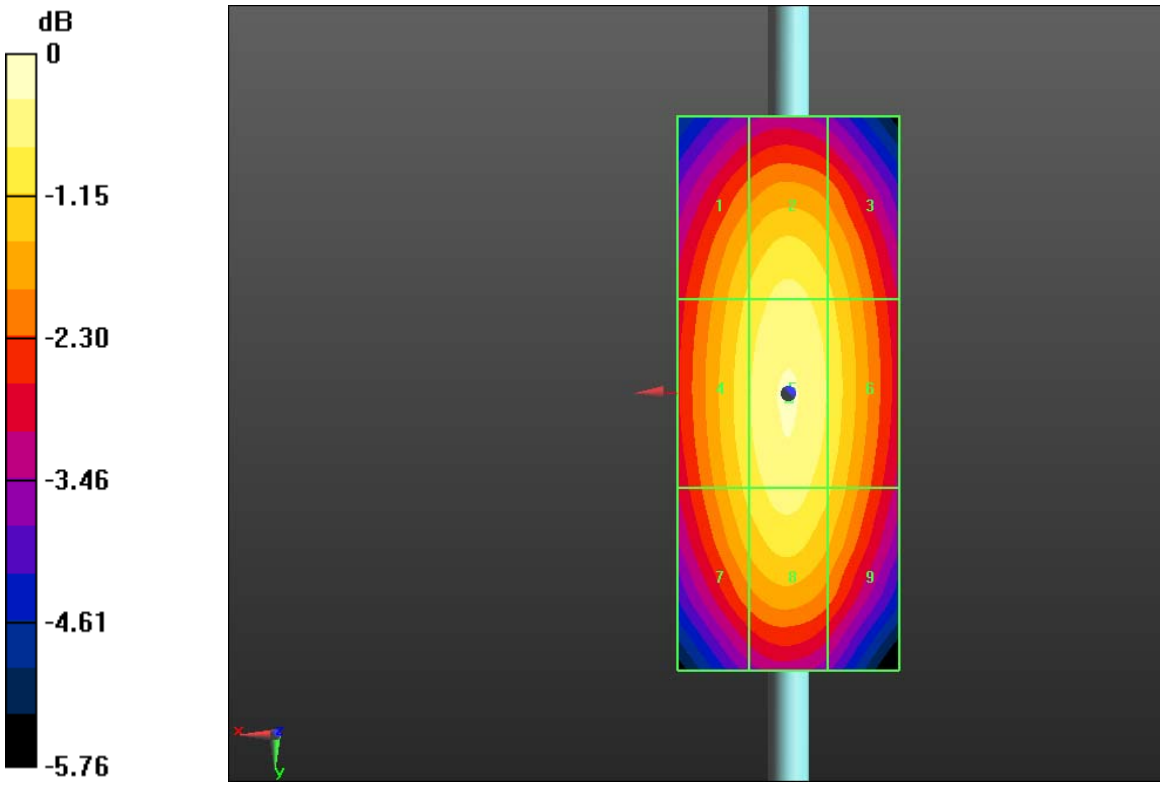
Dipole H-Field measurement with H3DV6 probe/H Scan - AM80%_1880_PMF/Hearing Aid Compatibility Test (41x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.10 V/m; Power Drift = -0.07 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.10 A/m
Near-field category: M4 (AWF 0 dB)

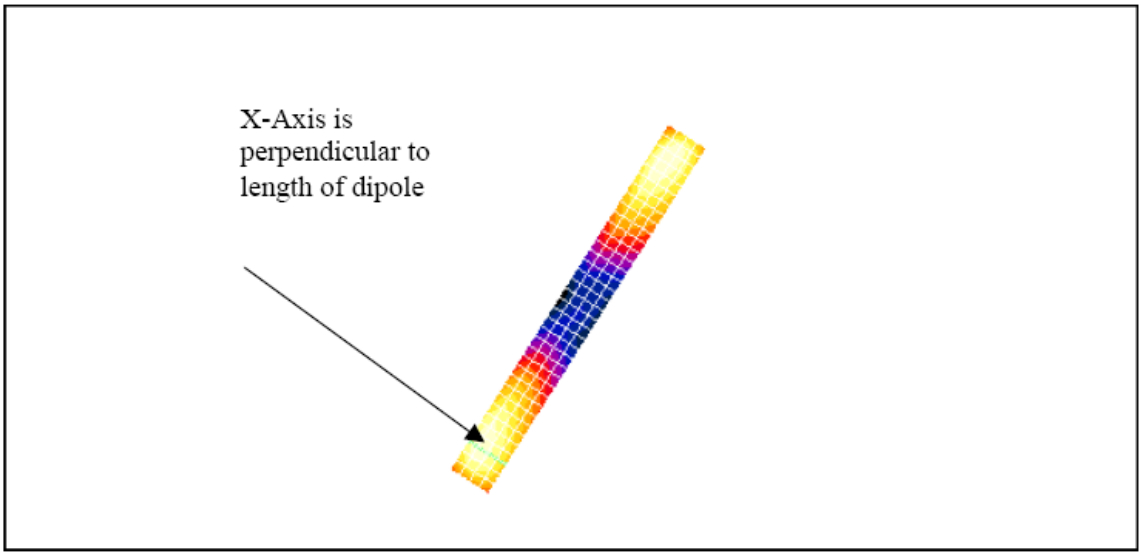
PMF scaled H-field

Grid 1 **M4** **0.09 A/m**	Grid 2 **M4** **0.09 A/m**	Grid 3 **M4** **0.09 A/m**
Grid 4 **M4** **0.09 A/m**	Grid 5 **M4** **0.10 A/m**	Grid 6 **M4** **0.09 A/m**
Grid 7 **M4** **0.09 A/m**	Grid 8 **M4** **0.09 A/m**	Grid 9 **M4** **0.09 A/m**

Cursor:
Total = 0.096 A/m
H Category: M4
Location: 0, 0, 4.7 mm



0 dB = 0.150A/m = -16.48 dB A/m



The green line in this figure shows the axis along which the points lie.

Comparison of 5mm and 2mm step sizes

An additional set of measurements was taken: dipole validations were performed using 5mm and 2mm step sizes. The delta between the two readings is insignificant for both field types (< 0.4% for E and 0% for H), demonstrating that 5mm is sufficient. The plots follow.

Date/Time: 14/07/2005 11:35:24 AM

Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3
Phantom section: H Device Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):
Measurement grid: dx=5mm, dy=5mm
Maximum value of Total (measured) = 134.8 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):
Measurement grid: dx=5mm, dy=5mm
Maximum value of Total field (slot averaged) = 131.0 V/m
Hearing Aid Near-Field Category: M2 (AWF 0 dB)

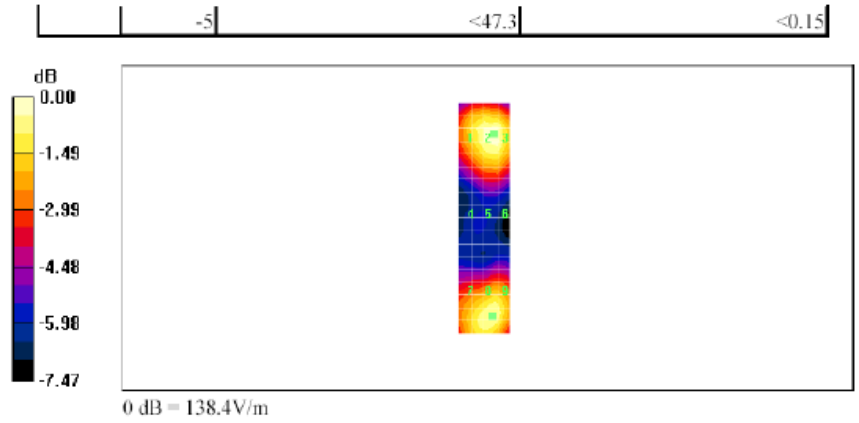
E in V/m (Time averaged)

Grid 1 **123.2**	Grid 2 **138.1**	Grid 3 **138.4**
Grid 4 **80.9**	Grid 5 **92.3**	Grid 6 **92.2**
Grid 7 **119.8**	Grid 8 **131.0**	Grid 9 **130.7**

E in V/m (Slot averaged)

Grid 1 **123.2**	Grid 2 **138.1**	Grid 3 **138.4**
Grid 4 **80.9**	Grid 5 **92.3**	Grid 6 **92.2**
Grid 7 **119.8**	Grid 8 **131.0**	Grid 9 **130.7**

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19



Date/Time: 14/07/2005 11:44:51 AM

Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_2mm step_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m^3
Phantom section: H Device Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):
Measurement grid: dx=2mm, dy=2mm
Maximum value of Total (measured) = 138.0 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):
Measurement grid: dx=2mm, dy=2mm
Maximum value of Total field (slot averaged) = 131.2 V/m
Hearing Aid Near-Field Category: M2 (AWF 0 dB)

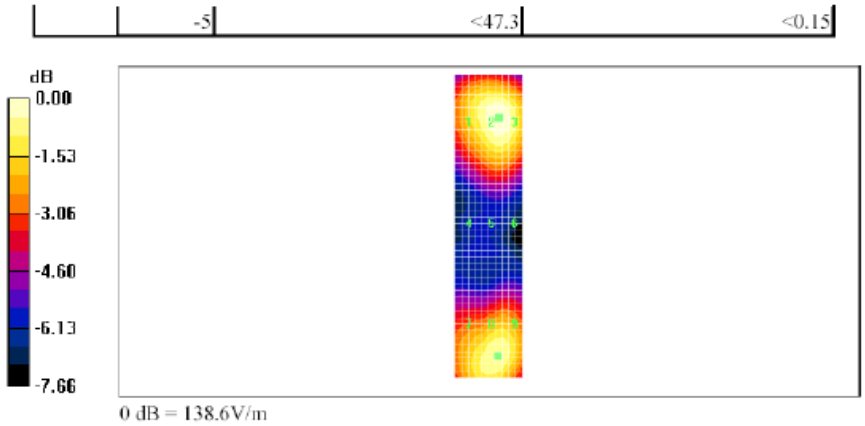
E in V/m (Time averaged)

Grid 1	Grid 2	Grid 3
123.1	**138.6**	**138.6**
Grid 4	Grid 5	Grid 6
81.4	**92.1**	**91.6**
Grid 7	Grid 8	Grid 9
121.3	**131.2**	**131.0**

E in V/m (Slot averaged)

Grid 1	Grid 2	Grid 3
123.1	**138.6**	**138.6**
Grid 4	Grid 5	Grid 6
81.4	**92.1**	**91.6**
Grid 7	Grid 8	Grid 9
121.3	**131.2**	**131.0**

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19



0 dB = 138.6V/m

Date/Time: 14/07/2005 12:43:02 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_5 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3
Phantom section: H Dipole Section

DASY4 Configuration:
- Probe: H3DV6 - SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1):
Measurement grid: dx=5mm, dy=5mm
Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1):
Measurement grid: dx=5mm, dy=5mm
Maximum value of Total field (slot averaged) = 0.406 A/m
Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged)

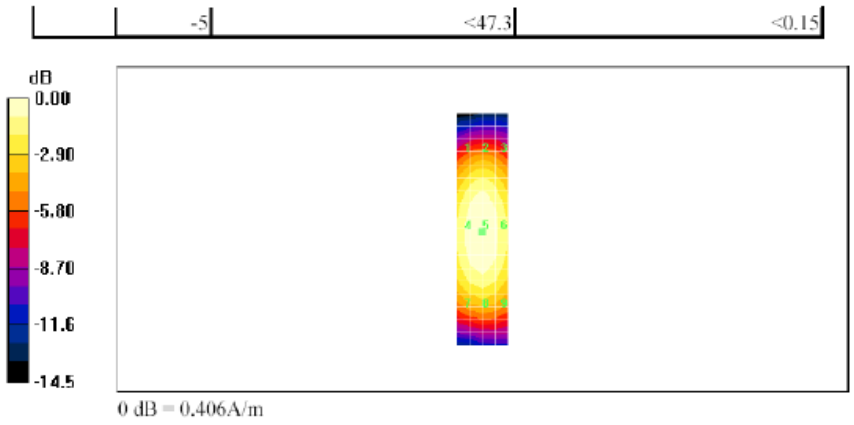
Grid 1	Grid 2	Grid 3
0.342	**0.359**	**0.344**
Grid 4	Grid 5	Grid 6
0.389	**0.406**	**0.389**
Grid 7	Grid 8	Grid 9
0.363	**0.378**	**0.363**

H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3
0.342	**0.359**	**0.344**
Grid 4	Grid 5	Grid 6
0.389	**0.406**	**0.389**
Grid 7	Grid 8	Grid 9
0.363	**0.378**	**0.363**

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

Date/Time: 14/07/2005 12:43:02 PM



Date/Time: 14/07/2005 12:53:40 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_2 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m^3
Phantom section: H Dipole Section

DASY4 Configuration:
- Probe: H3DV6 - SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1):
Measurement grid: dx=2mm, dy=2mm
Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):
Measurement grid: dx=2mm, dy=2mm
Maximum value of Total field (slot averaged) = 0.406 A/m
Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged)

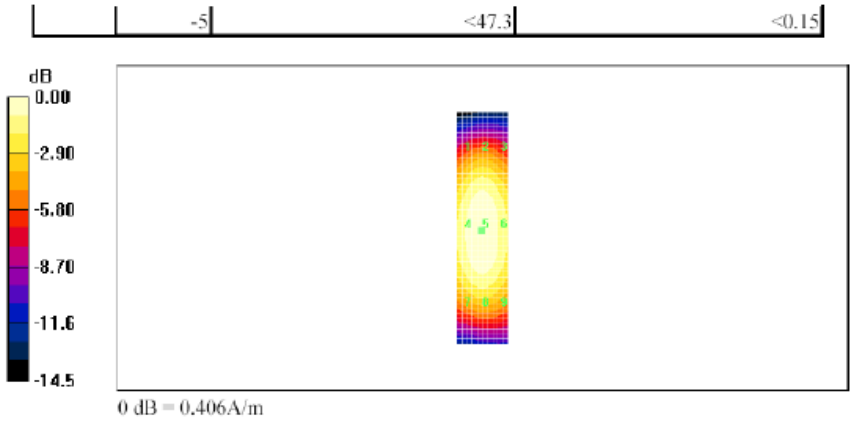
Grid 1	Grid 2	Grid 3
0.347	**0.361**	**0.348**
Grid 4	Grid 5	Grid 6
0.394	**0.406**	**0.391**
Grid 7	Grid 8	Grid 9
0.367	**0.380**	**0.365**

H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3
0.347	**0.361**	**0.348**
Grid 4	Grid 5	Grid 6
0.394	**0.406**	**0.391**
Grid 7	Grid 8	Grid 9
0.367	**0.380**	**0.365**

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

Date/Time: 14/07/2005 12:53:40 PM



0 dB = 0.406A/m

A.3 RF emission field plots

Date/Time: 12/18/2012 2:26:46 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM 850

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: GSM 850; Frequency: 824.2 MHz, Frequency: 836.8 MHz, Frequency: 848.8 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field GSM850 measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 80.46 V/m; Power Drift = -0.03 dB
PMR not calibrated. PMF = 3.000 is applied.
E-field emissions = 206.5 V/m
Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 **M3** **177.5 V/m**	Grid 2 **M3** **202.4 V/m**	Grid 3 **M3** **202.3 V/m**
Grid 4 **M3** **177.0 V/m**	Grid 5 **M3** **206.5 V/m**	Grid 6 **M3** **206.4 V/m**

Grid 7 **M3** **175.9 V/m**	Grid 8 **M3** **203.7 V/m**	Grid 9 **M3** **203.4 V/m**

Cursor:

Total = 206.5 V/m
E Category: M3
Location: -8, 0.5, 8.7 mm

Device E-Field GSM850 measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 78.44 V/m; Power Drift = -0.08 dB
PMR not calibrated. PMF = 3.000 is applied.
E-field emissions = 204.7 V/m
Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 **M3** **163.5 V/m**	Grid 2 **M3** **196.2 V/m**	Grid 3 **M3** **196.2 V/m**
Grid 4 **M3** **167.5 V/m**	Grid 5 **M3** **204.7 V/m**	Grid 6 **M3** **204.6 V/m**
Grid 7 **M3** **173.4 V/m**	Grid 8 **M3** **203.8 V/m**	Grid 9 **M3** **203.7 V/m**

Cursor:

Total = 204.7 V/m
E Category: M3
Location: -7.5, 5, 8.7 mm

Device E-Field GSM850 measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 73.32 V/m; Power Drift = -0.04 dB
PMR not calibrated. PMF = 3.000 is applied.
E-field emissions = 194.2 V/m

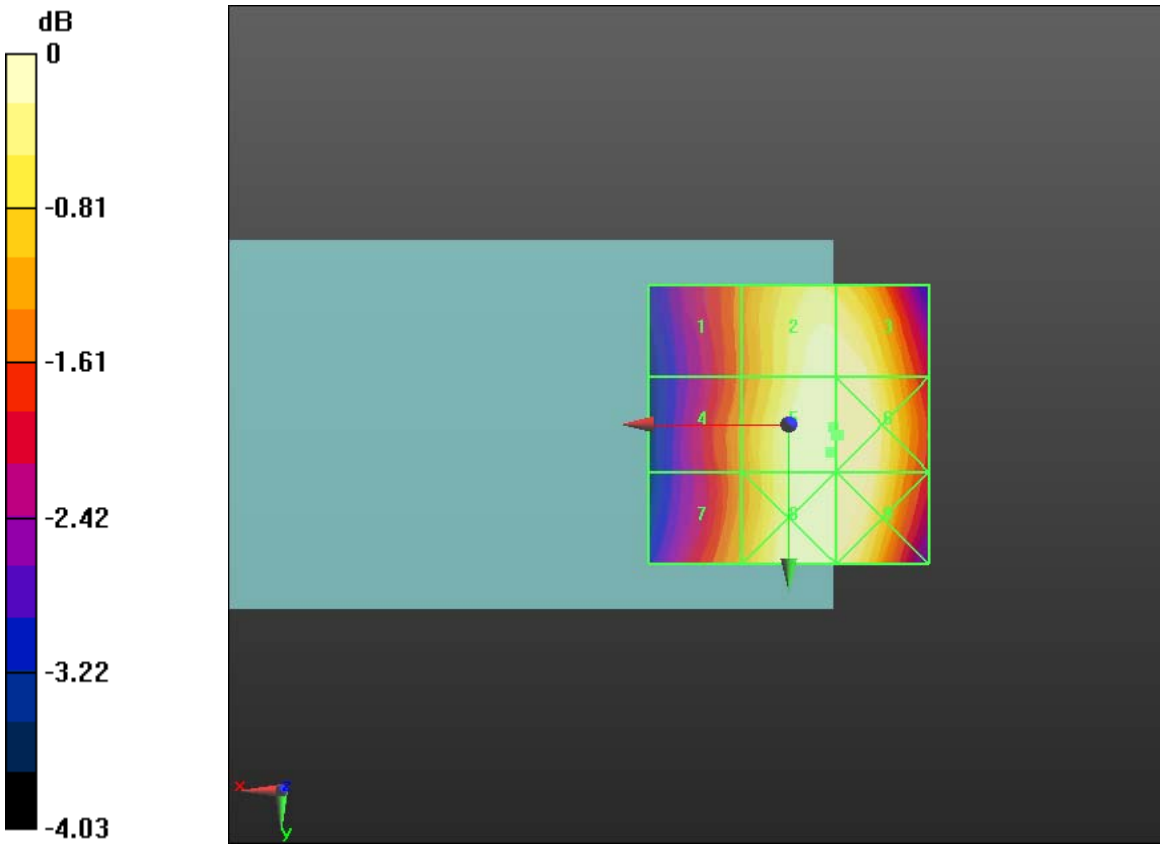
Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 **M3** **153.6 V/m**	Grid 2 **M3** **190.0 V/m**	Grid 3 **M3** **190.0 V/m**
Grid 4 **M3** **155.2 V/m**	Grid 5 **M3** **194.2 V/m**	Grid 6 **M3** **194.2 V/m**
Grid 7 **M3** **158.0 V/m**	Grid 8 **M3** **191.9 V/m**	Grid 9 **M3** **191.9 V/m**

Cursor:

Total = 194.2 V/m
E Category: M3
Location: -9, 2, 8.7 mm



0 dB = 198.3V/m = 45.95 dB V/m

Date/Time: 12/18/2012 10:12:14 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM835_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: GSM 850; Frequency: 824.2 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field GSM850 measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 74.15 V/m; Power Drift = -0.01 dB
PMR not calibrated. PMF = 3.000 is applied.
E-field emissions = 187.9 V/m
Near-field category: M3 (AWF -5 dB)

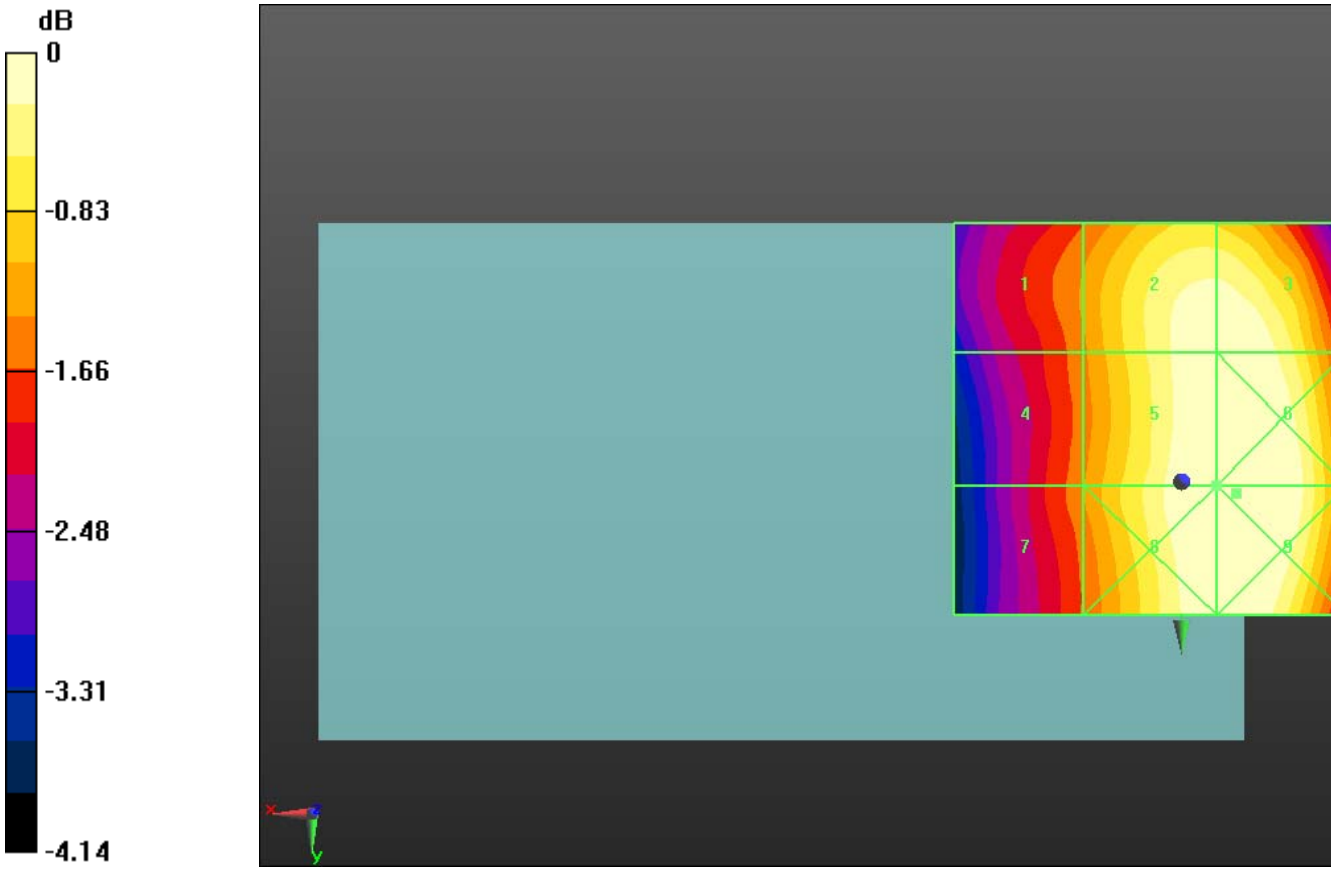
PMF scaled E-field

Grid 1 **M3** **156.1 V/m**	Grid 2 **M3** **182.2 V/m**	Grid 3 **M3** **182.4 V/m**
Grid 4 **M3** **154.9 V/m**	Grid 5 **M3** **187.9 V/m**	Grid 6 **M3** **189.1 V/m**
Grid 7 **M3**	Grid 8 **M3**	Grid 9 **M3**

155.0 V/m	**188.0 V/m**	**189.2 V/m**

Cursor:

Total = 189.2 V/m
E Category: M3
Location: -7, 1.5, 8.7 mm



0 dB = 181.7V/m = 45.19 dB V/m

Date/Time: 12/18/2012 3:07:07 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_band V

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: WCDMA FDD V; Frequency: 826.4 MHz, Frequency: 836.4 MHz, Frequency: 846.6 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field UMTS band V measurement with ER probe 2 2/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 82.24 V/m; Power Drift = -0.01 dB
PMR not calibrated. PMF = 1.070 is applied.
E-field emissions = 75.80 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **61.63 V/m**	Grid 2 **M4** **73.00 V/m**	Grid 3 **M4** **73.00 V/m**
Grid 4 **M4** **62.87 V/m**	Grid 5 **M4** **75.80 V/m**	Grid 6 **M4** **75.79 V/m**
Grid 7 **M4**	Grid 8 **M4**	Grid 9 **M4**

64.80 V/m	75.31 V/m	75.29 V/m

Cursor:
Total = 75.799 V/m
E Category: M4
Location: -8, 4.5, 8.7 mm

Device E-Field UMTS band V measurement with ER probe 2 2/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 83.58 V/m; Power Drift = -0.02 dB
PMR not calibrated. PMF = 1.070 is applied.
E-field emissions = 79.83 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **60.89 V/m**	Grid 2 **M4** **75.98 V/m**	Grid 3 **M4** **76.01 V/m**
Grid 4 **M4** **63.40 V/m**	Grid 5 **M4** **79.83 V/m**	Grid 6 **M4** **79.83 V/m**
Grid 7 **M4** **66.19 V/m**	Grid 8 **M4** **79.59 V/m**	Grid 9 **M4** **79.59 V/m**

Cursor:
Total = 79.828 V/m
E Category: M4
Location: -8.5, 5.5, 8.7 mm

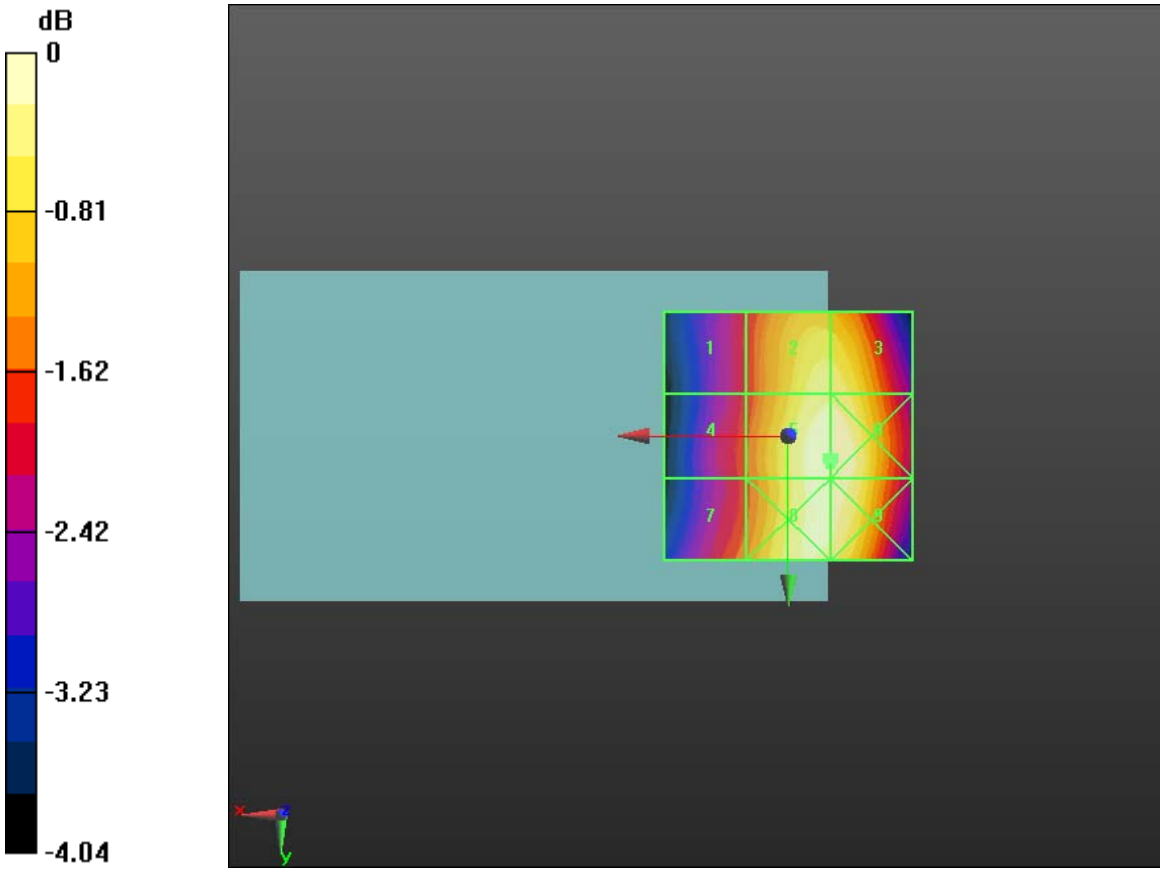
Device E-Field UMTS band V measurement with ER probe 2 2/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 89.08 V/m; Power Drift = -0.13 dB
PMR not calibrated. PMF = 1.070 is applied.
E-field emissions = 82.50 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **65.22 V/m**	Grid 2 **M4** **79.36 V/m**	Grid 3 **M4** **79.36 V/m**
Grid 4 **M4** **66.57 V/m**	Grid 5 **M4** **82.50 V/m**	Grid 6 **M4** **82.56 V/m**
Grid 7 **M4** **69.34 V/m**	Grid 8 **M4** **81.94 V/m**	Grid 9 **M4** **81.99 V/m**

Cursor:
Total = 82.560 V/m
E Category: M4
Location: -9, 4.5, 8.7 mm



0 dB = 75.800V/m = 37.59 dB V/m

Date/Time: 12/18/2012 2:44:01 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM 1900

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: GSM 1900; Frequency: 1850.2 MHz, Frequency: 1880 MHz, Frequency: 1909.8 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field GSM 1900 measurement with ER probe 2/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 15.83 V/m; Power Drift = 0.20 dB
PMR not calibrated. PMF = 2.850 is applied.
E-field emissions = 77.90 V/m
Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 **M3** **72.78 V/m**	Grid 2 **M3** **77.90 V/m**	Grid 3 **M3** **73.98 V/m**
Grid 4 **M4** **43.29 V/m**	Grid 5 **M3** **55.32 V/m**	Grid 6 **M3** **57.82 V/m**

Grid 7 **M3** **67.31 V/m**	Grid 8 **M2** **85.44 V/m**	Grid 9 **M2** **85.44 V/m**

Cursor:

Total = 85.438 V/m
E Category: M2
Location: -8.5, 25, 8.7 mm

Device E-Field GSM 1900 measurement with ER probe 2/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 16.02 V/m; Power Drift = -0.02 dB
PMR not calibrated. PMF = 2.850 is applied.
E-field emissions = 71.76 V/m
Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 **M3** **66.31 V/m**	Grid 2 **M3** **71.76 V/m**	Grid 3 **M3** **71.39 V/m**
Grid 4 **M4** **42.05 V/m**	Grid 5 **M3** **50.97 V/m**	Grid 6 **M3** **53.79 V/m**
Grid 7 **M3** **55.96 V/m**	Grid 8 **M3** **74.91 V/m**	Grid 9 **M3** **74.91 V/m**

Cursor:

Total = 74.910 V/m
E Category: M3
Location: -8.5, 25, 8.7 mm

Device E-Field GSM 1900 measurement with ER probe 2/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 17.00 V/m; Power Drift = -0.17 dB
PMR not calibrated. PMF = 2.850 is applied.
E-field emissions = 68.16 V/m

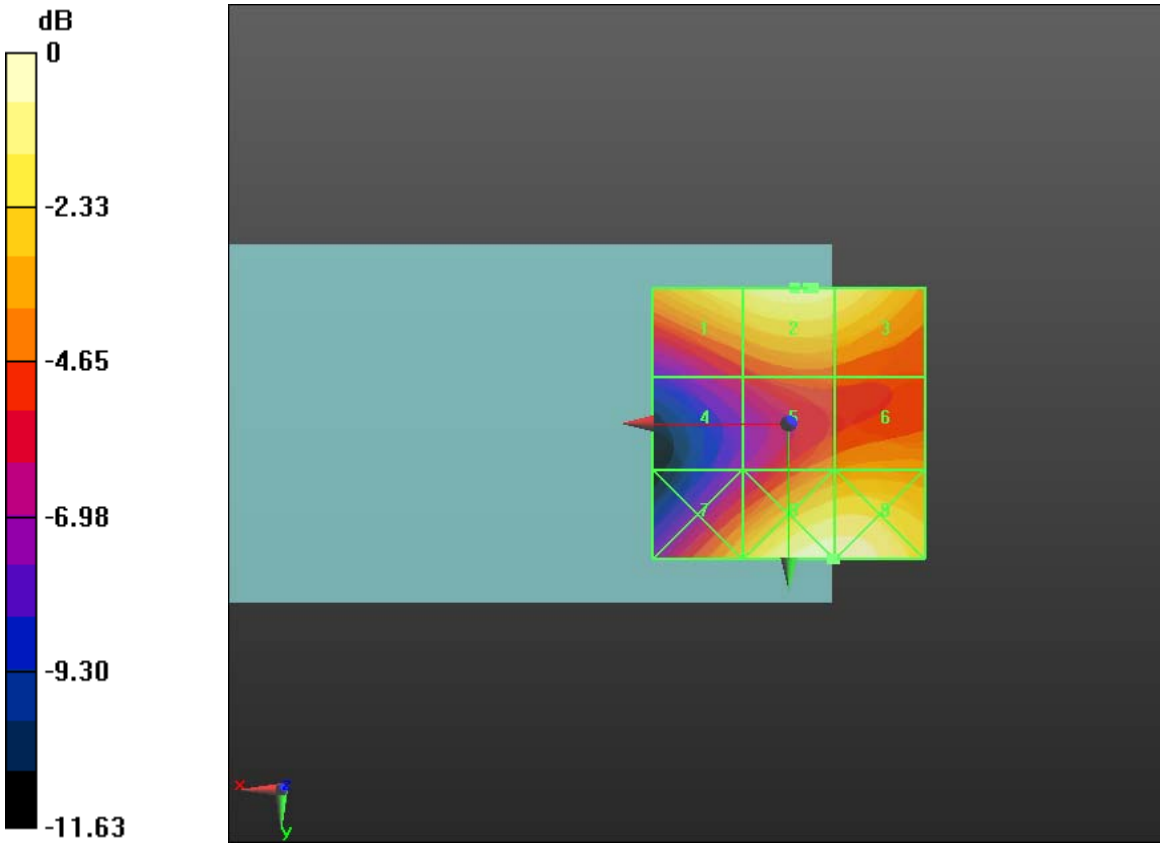
Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

Grid 1 **M3** **62.92 V/m**	Grid 2 **M3** **68.16 V/m**	Grid 3 **M3** **67.57 V/m**
Grid 4 **M4** **42.77 V/m**	Grid 5 **M3** **48.94 V/m**	Grid 6 **M3** **50.06 V/m**
Grid 7 **M3** **50.61 V/m**	Grid 8 **M3** **68.65 V/m**	Grid 9 **M3** **68.63 V/m**

Cursor:

Total = 68.645 V/m
E Category: M3
Location: -8, 25, 8.7 mm



0 dB = 86.370V/m = 38.73 dB V/m

Date/Time: 12/18/2012 10:23:44 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM1900_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: GSM 1900; Frequency: 1850.2 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field GSM 1900 measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_telecoil/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 15.47 V/m; Power Drift = 0.07 dB
PMR not calibrated. PMF = 2.850 is applied.
E-field emissions = 69.05 V/m
Near-field category: M3 (AWF -5 dB)

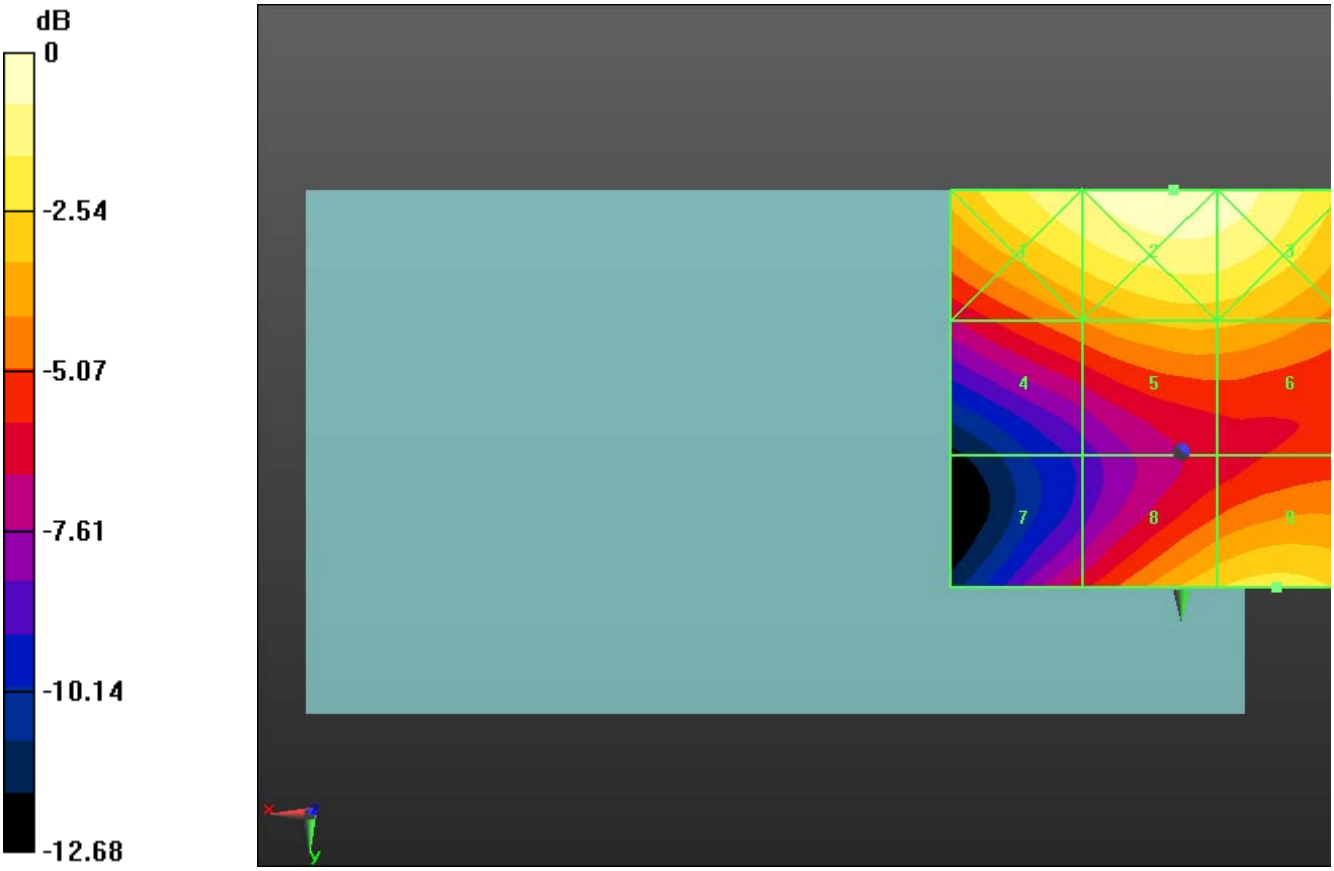
PMF scaled E-field

Grid 1 **M3** **80.16 V/m**	Grid 2 **M2** **87.26 V/m**	Grid 3 **M2** **85.73 V/m**
Grid 4 **M3** **54.37 V/m**	Grid 5 **M3** **61.95 V/m**	Grid 6 **M3** **61.64 V/m**
Grid 7 **M4**	Grid 8 **M3**	Grid 9 **M3**

43.48 V/m	**65.41 V/m**	**69.05 V/m**

Cursor:

Total = 87.258 V/m
E Category: M2
Location: 1, -33, 8.7 mm



0 dB = 88.210V/m = 38.91 dB V/m

Date/Time: 12/18/2012 3:22:04 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_UMTS_band II

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz, Frequency: 1880 MHz, Frequency: 1907.6 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field UMTS band II measurement with ER probe 2 2 2/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Device Reference Point: 0, 0, -6.3 mm
Reference Value = 25.00 V/m; Power Drift = 0.07 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 30.85 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **28.88 V/m**	Grid 2 **M4** **30.85 V/m**	Grid 3 **M4** **29.71 V/m**
Grid 4 **M4** **18.87 V/m**	Grid 5 **M4** **24.00 V/m**	Grid 6 **M4** **24.37 V/m**
Grid 7 **M4**	Grid 8 **M4**	Grid 9 **M4**

26.14 V/m	**33.93 V/m**	**33.90 V/m**

Cursor:
Total = 33.930 V/m
E Category: M4
Location: -7.5, 25, 8.7 mm

Device E-Field UMTS band II measurement with ER probe 2 2 2/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_Mid_Chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 24.38 V/m; Power Drift = -0.15 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 29.88 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **27.62 V/m**	Grid 2 **M4** **29.88 V/m**	Grid 3 **M4** **29.22 V/m**
Grid 4 **M4** **17.29 V/m**	Grid 5 **M4** **25.62 V/m**	Grid 6 **M4** **25.96 V/m**
Grid 7 **M4** **26.93 V/m**	Grid 8 **M4** **35.72 V/m**	Grid 9 **M4** **35.67 V/m**

Cursor:
Total = 35.724 V/m
E Category: M4
Location: -7.5, 25, 8.7 mm

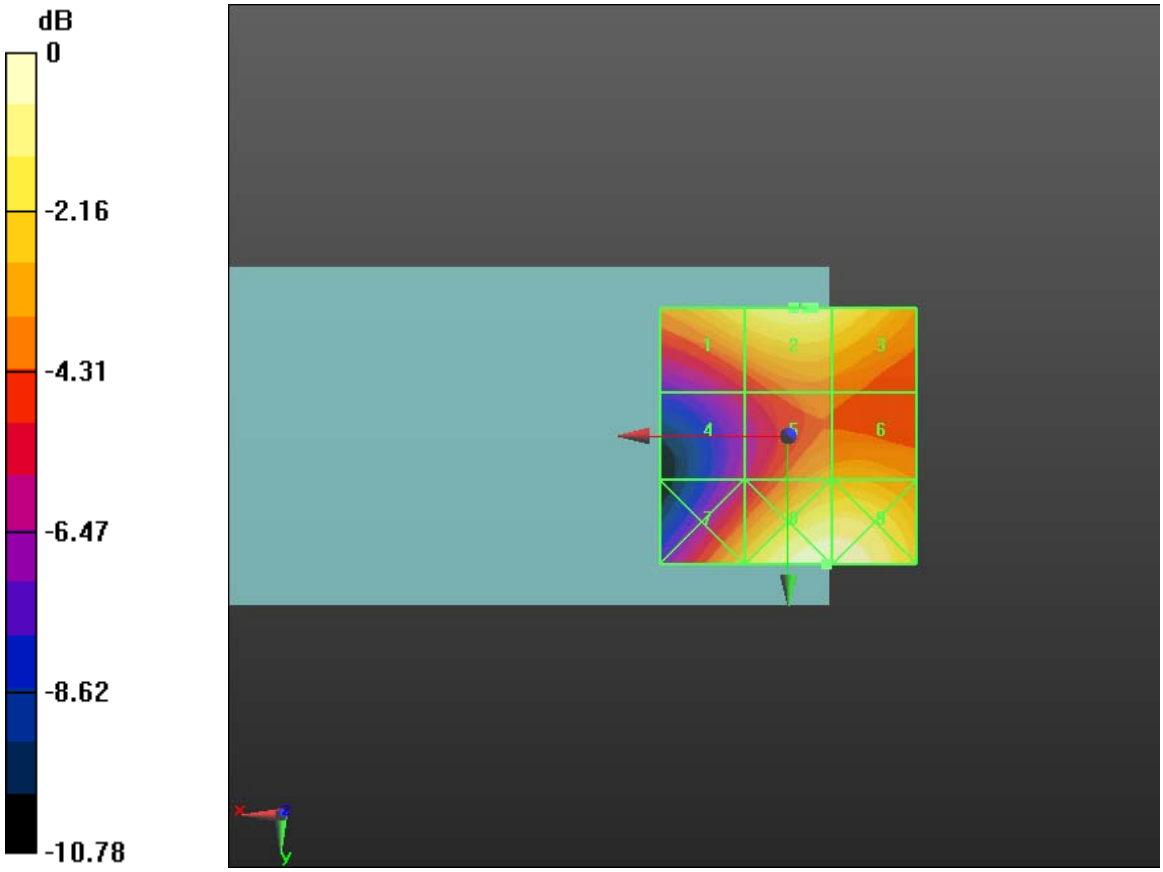
Device E-Field UMTS band II measurement with ER probe 2 2 2/E Scan - ER3D - 2007: 15 mm from Probe Center to the Device_High_Chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 21.66 V/m; Power Drift = 0.02 dB
PMR not calibrated. PMF = 1.000 is applied.
E-field emissions = 32.47 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **29.36 V/m**	Grid 2 **M4** **32.47 V/m**	Grid 3 **M4** **31.96 V/m**
Grid 4 **M4** **17.63 V/m**	Grid 5 **M4** **25.37 V/m**	Grid 6 **M4** **25.89 V/m**
Grid 7 **M4** **26.87 V/m**	Grid 8 **M4** **36.79 V/m**	Grid 9 **M4** **36.75 V/m**

Cursor:
Total = 36.786 V/m
E Category: M4
Location: -7.5, 25, 8.7 mm



0 dB = 33.930V/m = 30.61 dB V/m

Date/Time: 12/18/2012 10:49:07 PM

Test Laboratory: RIM Testing Services

HAC RF_E-Field_GSM1900_2100_Battery

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: GSM 1900; Frequency: 1850.2 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 1/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device E-Field GSM 1900 measurement with ER probe/E Scan - ER3D - 2007: 15 mm from Probe Center to Device_Low_Chan_2100 Battery/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 16.16 V/m; Power Drift = 0.04 dB
PMR not calibrated. PMF = 2.850 is applied.
E-field emissions = 79.89 V/m
Near-field category: M3 (AWF -5 dB)

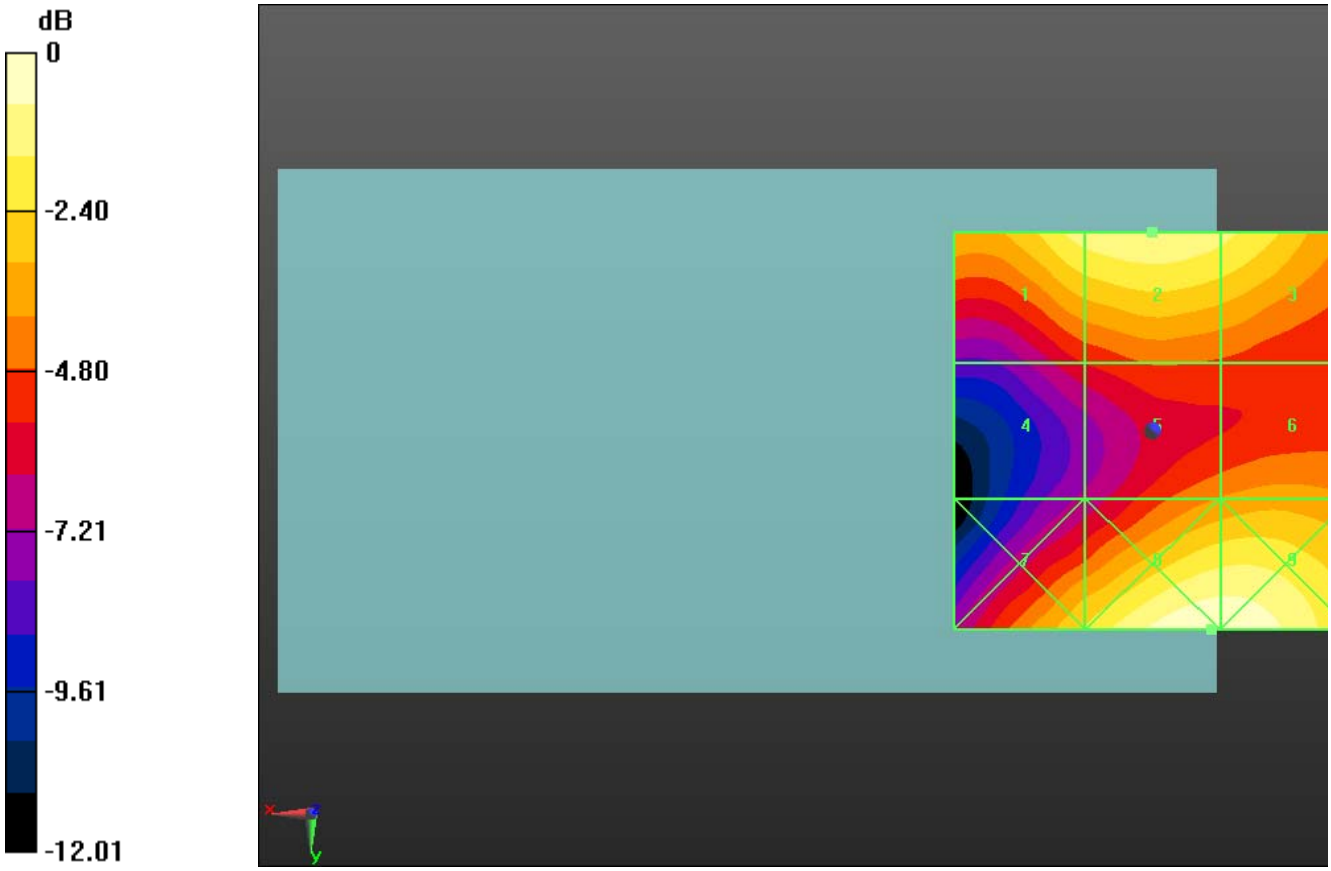
PMF scaled E-field

Grid 1 **M3** **76.48 V/m**	Grid 2 **M3** **79.89 V/m**	Grid 3 **M3** **75.17 V/m**
Grid 4 **M4** **46.07 V/m**	Grid 5 **M3** **55.51 V/m**	Grid 6 **M3** **58.20 V/m**
Grid 7 **M3**	Grid 8 **M2**	Grid 9 **M2**

67.10 V/m	**86.51 V/m**	**86.42 V/m**

Cursor:

Total = 86.508 V/m
E Category: M2
Location: -7.5, 25, 8.7 mm



0 dB = 87.450V/m = 38.84 dB V/m

Date/Time: 12/18/2012 4:17:35 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM 850

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: GSM 850; Frequency: 824.2 MHz, Frequency: 836.8 MHz, Frequency: 848.8 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field GSM 850_meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07 V/m; Power Drift = 0.07 dB
PMR not calibrated. PMF = 2.890 is applied.
H-field emissions = 0.42 A/m
Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

Grid 1 **M4** **0.42 A/m**	Grid 2 **M4** **0.30 A/m**	Grid 3 **M4** **0.19 A/m**
Grid 4 **M4** **0.36 A/m**	Grid 5 **M4** **0.26 A/m**	Grid 6 **M4** **0.16 A/m**
Grid 7 **M4**	Grid 8 **M4**	Grid 9 **M4**

0.36 A/m	**0.26 A/m**	**0.16 A/m**

Cursor:

Total = 0.419 A/m
H Category: M4
Location: 25, -25, 8.7 mm

Device H-Field GSM 850_meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07 V/m; Power Drift = 0.05 dB
PMR not calibrated. PMF = 2.890 is applied.
H-field emissions = 0.41 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

Grid 1 **M4** **0.41 A/m**	Grid 2 **M4** **0.32 A/m**	Grid 3 **M4** **0.21 A/m**
Grid 4 **M4** **0.36 A/m**	Grid 5 **M4** **0.27 A/m**	Grid 6 **M4** **0.18 A/m**
Grid 7 **M4** **0.37 A/m**	Grid 8 **M4** **0.27 A/m**	Grid 9 **M4** **0.17 A/m**

Cursor:

Total = 0.414 A/m
H Category: M4
Location: 25, -25, 8.7 mm

Device H-Field GSM 850_meausrement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.08 V/m; Power Drift = 0.22 dB
PMR not calibrated. PMF = 2.890 is applied.
H-field emissions = 0.42 A/m

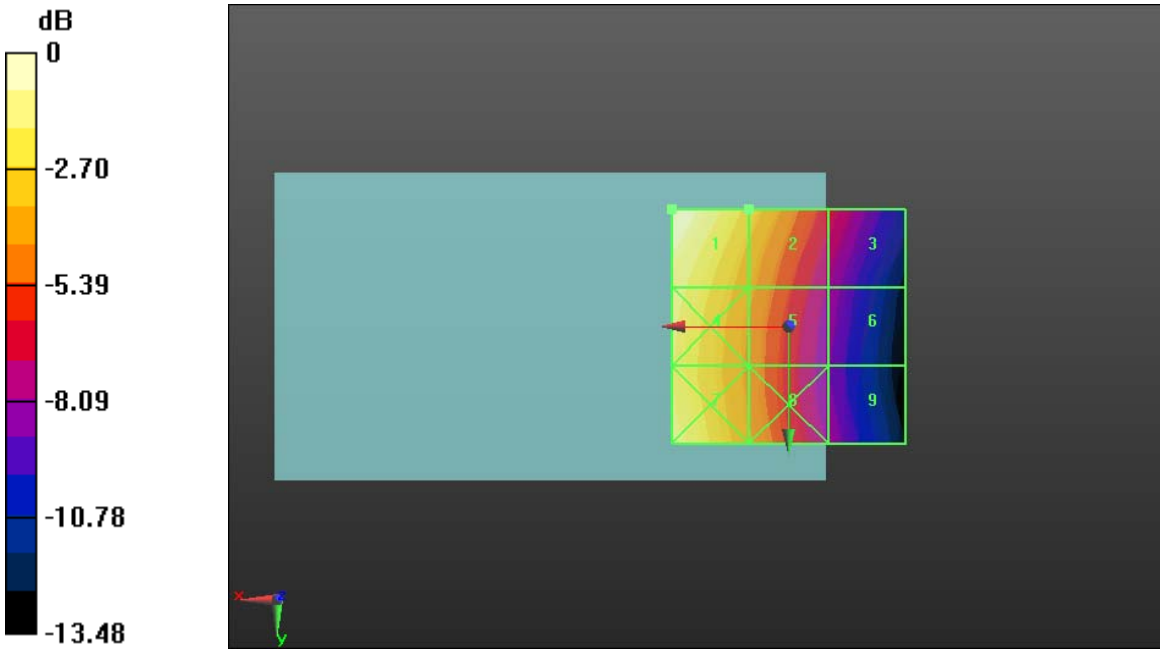
Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

Grid 1 **M4** **0.42 A/m**	Grid 2 **M4** **0.32 A/m**	Grid 3 **M4** **0.21 A/m**
Grid 4 **M4** **0.37 A/m**	Grid 5 **M4** **0.28 A/m**	Grid 6 **M4** **0.19 A/m**
Grid 7 **M4** **0.38 A/m**	Grid 8 **M4** **0.29 A/m**	Grid 9 **M4** **0.20 A/m**

Cursor:

Total = 0.418 A/m
H Category: M4
Location: 25, -25, 8.7 mm



0 dB = 0.420A/m = -7.54 dB A/m

Date/Time: 12/18/2012 4:35:47 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM 850_telecoil_center

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: GSM 850; Frequency: 824.2 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field GSM 850_measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_Centre_Telecoil/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07 V/m; Power Drift = 0.06 dB
PMR not calibrated. PMF = 2.890 is applied.
H-field emissions = 0.46 A/m
Near-field category: M3 (AWF -5 dB)

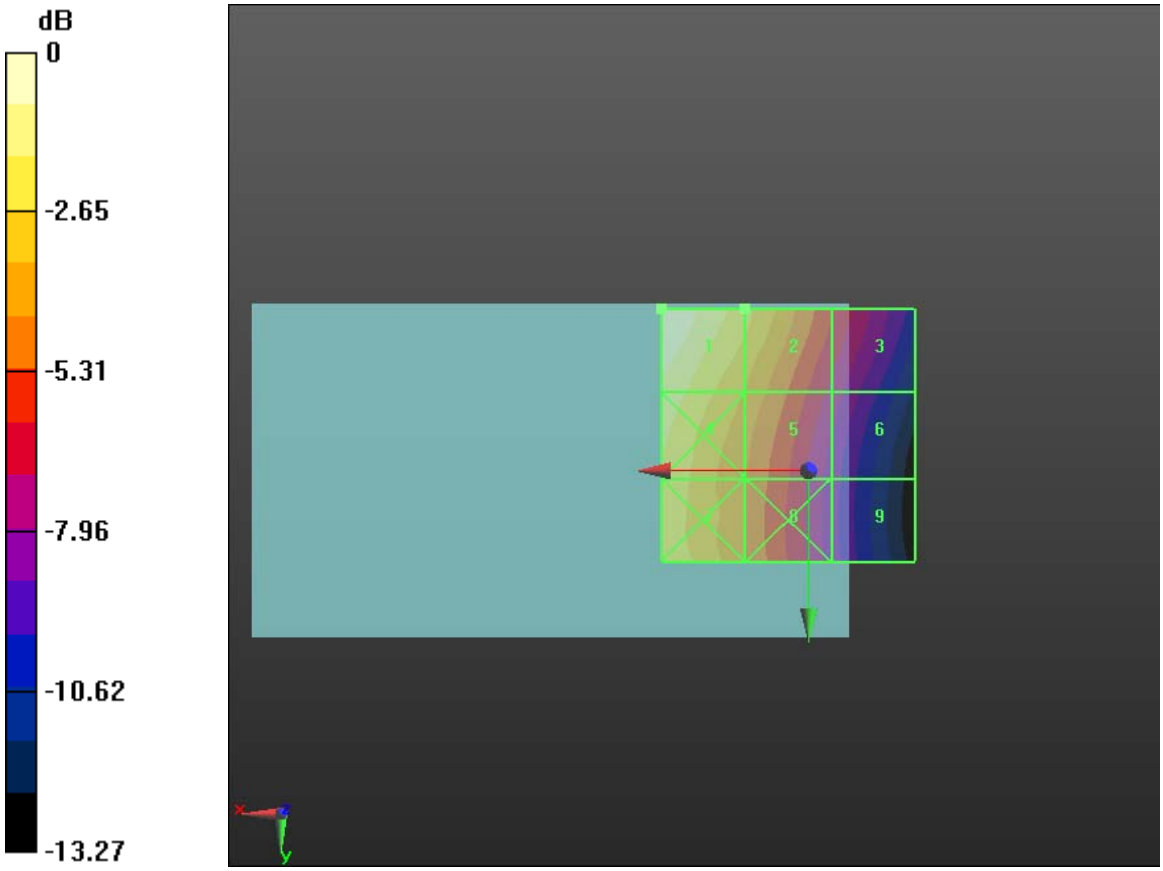
PMF scaled H-field

Grid 1 **M3** **0.46 A/m**	Grid 2 **M4** **0.34 A/m**	Grid 3 **M4** **0.22 A/m**
Grid 4 **M4** **0.40 A/m**	Grid 5 **M4** **0.30 A/m**	Grid 6 **M4** **0.19 A/m**
Grid 7 **M4**	Grid 8 **M4**	Grid 9 **M4**

0.36 A/m	**0.27 A/m**	**0.17 A/m**

Cursor:

Total = 0.456 A/m
H Category: M3
Location: 29, -32, 8.7 mm



0 dB = 0.450A/m = -6.94 dB A/m

Date/Time: 12/18/2012 6:34:22 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_V

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: WCDMA FDD V; Frequency: 826.4 MHz, Frequency: 836.4 MHz, Frequency: 846.6 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field UMTS band V_measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07 V/m; Power Drift = -0.07 dB
PMR not calibrated. PMF = 1.090 is applied.
H-field emissions = 0.16 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.16 A/m**	Grid 2 **M4** **0.12 A/m**	Grid 3 **M4** **0.08 A/m**
Grid 4 **M4** **0.14 A/m**	Grid 5 **M4** **0.10 A/m**	Grid 6 **M4** **0.07 A/m**
Grid 7 **M4**	Grid 8 **M4**	Grid 9 **M4**

0.14 A/m	**0.10 A/m**	**0.06 A/m**

Cursor:
Total = 0.162 A/m
H Category: M4
Location: 25, -25, 8.7 mm

Device H-Field UMTS band V_measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.08 V/m; Power Drift = 0.07 dB
PMR not calibrated. PMF = 1.090 is applied.
H-field emissions = 0.17 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.17 A/m**	Grid 2 **M4** **0.13 A/m**	Grid 3 **M4** **0.09 A/m**
Grid 4 **M4** **0.15 A/m**	Grid 5 **M4** **0.11 A/m**	Grid 6 **M4** **0.08 A/m**
Grid 7 **M4** **0.15 A/m**	Grid 8 **M4** **0.11 A/m**	Grid 9 **M4** **0.07 A/m**

Cursor:
Total = 0.172 A/m
H Category: M4
Location: 25, -25, 8.7 mm

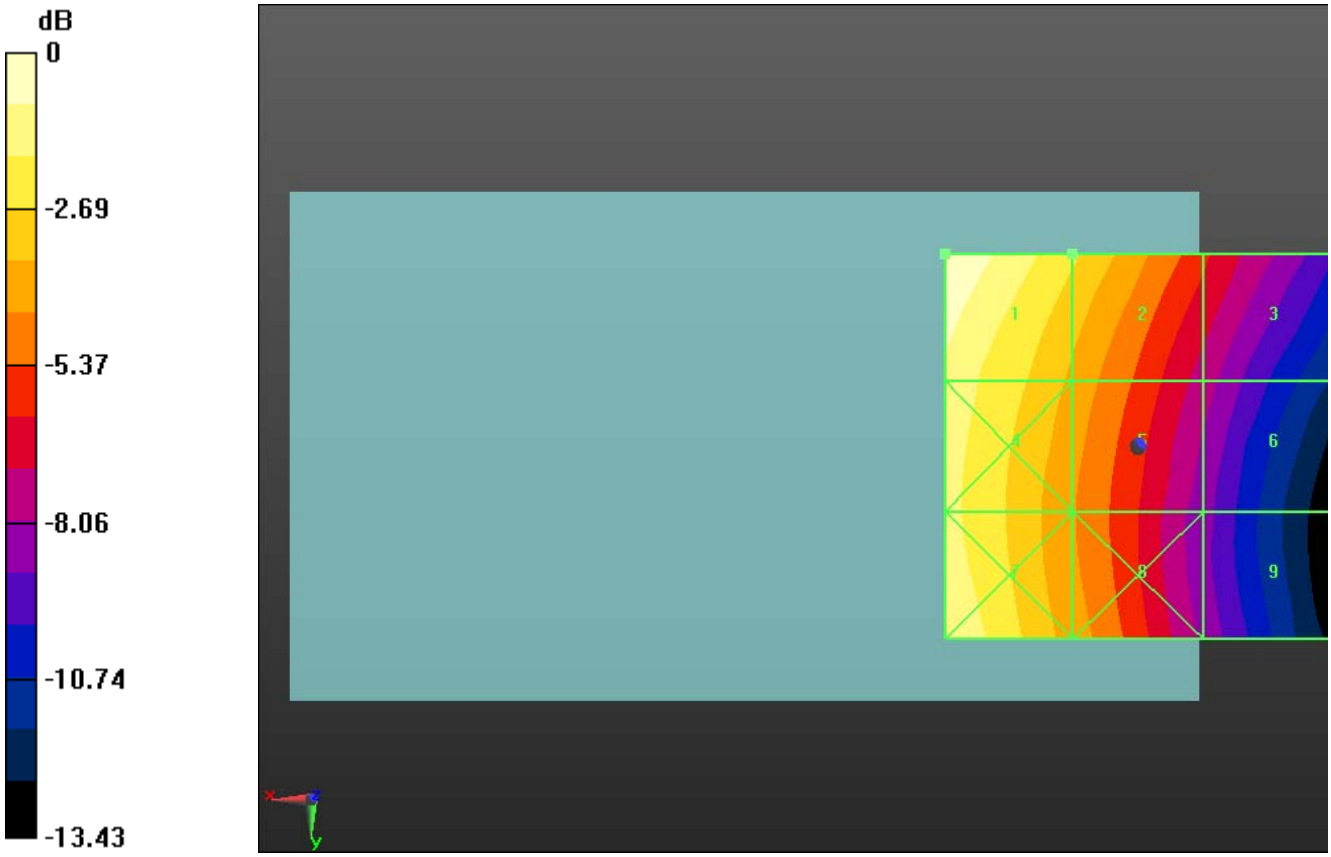
Device H-Field UMTS band V_measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.10 V/m; Power Drift = -0.19 dB
PMR not calibrated. PMF = 1.090 is applied.
H-field emissions = 0.19 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.19 A/m**	Grid 2 **M4** **0.14 A/m**	Grid 3 **M4** **0.10 A/m**
Grid 4 **M4** **0.16 A/m**	Grid 5 **M4** **0.13 A/m**	Grid 6 **M4** **0.09 A/m**
Grid 7 **M4** **0.17 A/m**	Grid 8 **M4** **0.13 A/m**	Grid 9 **M4** **0.08 A/m**

Cursor:
Total = 0.189 A/m
H Category: M4
Location: 25, -25, 8.7 mm



0 dB = 0.160A/m = -15.92 dB A/m

Date/Time: 12/18/2012 4:46:56 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM 1900

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: GSM 1900; Frequency: 1880 MHz, Frequency: 1909.8 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA; Serial: Not Specified
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field GSM 1900_measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07 V/m; Power Drift = 0.13 dB
PMR not calibrated. PMF = 2.860 is applied.
H-field emissions = 0.19 A/m
Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

Grid 1 **M3** **0.21 A/m**	Grid 2 **M3** **0.19 A/m**	Grid 3 **M3** **0.19 A/m**
Grid 4 **M3** **0.16 A/m**	Grid 5 **M3** **0.19 A/m**	Grid 6 **M3** **0.19 A/m**
Grid 7 **M3**	Grid 8 **M3**	Grid 9 **M3**

0.18 A/m	**0.18 A/m**	**0.18 A/m**

Cursor:

Total = 0.207 A/m
H Category: M3
Location: 25, -25, 8.7 mm

Device H-Field GSM 1900_measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07 V/m; Power Drift = -0.03 dB
PMR not calibrated. PMF = 2.860 is applied.
H-field emissions = 0.19 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

Grid 1 **M3** **0.21 A/m**	Grid 2 **M3** **0.19 A/m**	Grid 3 **M3** **0.19 A/m**
Grid 4 **M3** **0.16 A/m**	Grid 5 **M3** **0.19 A/m**	Grid 6 **M3** **0.19 A/m**
Grid 7 **M3** **0.18 A/m**	Grid 8 **M3** **0.18 A/m**	Grid 9 **M3** **0.18 A/m**

Cursor:

Total = 0.213 A/m
H Category: M3
Location: 25, -25, 8.7 mm

Device H-Field GSM 1900_measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07 V/m; Power Drift = -0.16 dB
PMR not calibrated. PMF = 2.860 is applied.
H-field emissions = 0.18 A/m

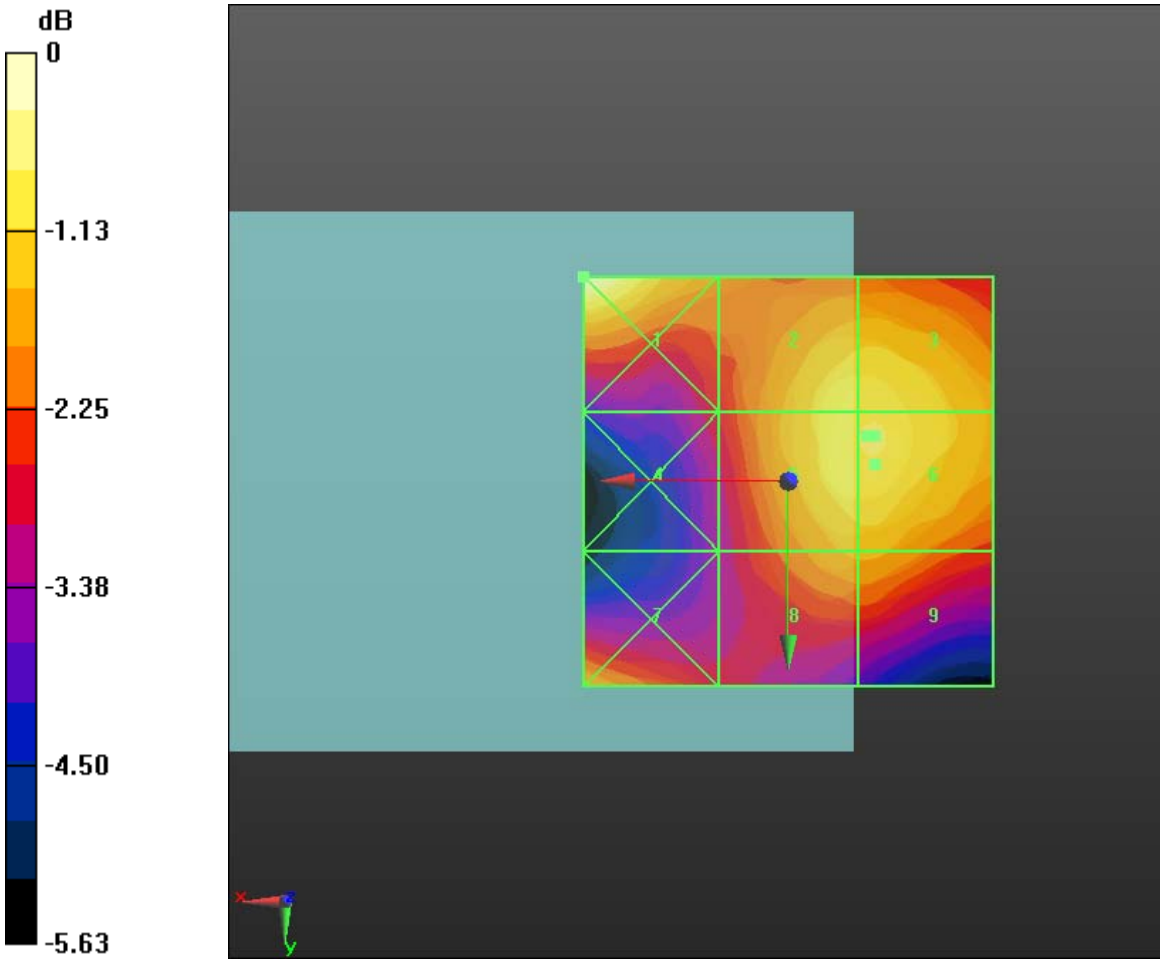
Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

Grid 1 **M3** **0.19 A/m**	Grid 2 **M3** **0.18 A/m**	Grid 3 **M3** **0.18 A/m**
Grid 4 **M3** **0.14 A/m**	Grid 5 **M3** **0.18 A/m**	Grid 6 **M3** **0.18 A/m**
Grid 7 **M3** **0.16 A/m**	Grid 8 **M3** **0.17 A/m**	Grid 9 **M3** **0.17 A/m**

Cursor:

Total = 0.190 A/m
H Category: M3
Location: 25, -25, 8.7 mm



0 dB = 0.210A/m = -13.56 dB A/m

Date/Time: 12/18/2012 5:04:53 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM1900_Telecoil

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: GSM 1900; Frequency: 1880 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field GSM 1900_measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_Centre_Telecoil/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07 V/m; Power Drift = 0.19 dB
PMR not calibrated. PMF = 2.860 is applied.
H-field emissions = 0.20 A/m
Near-field category: M3 (AWF -5 dB)

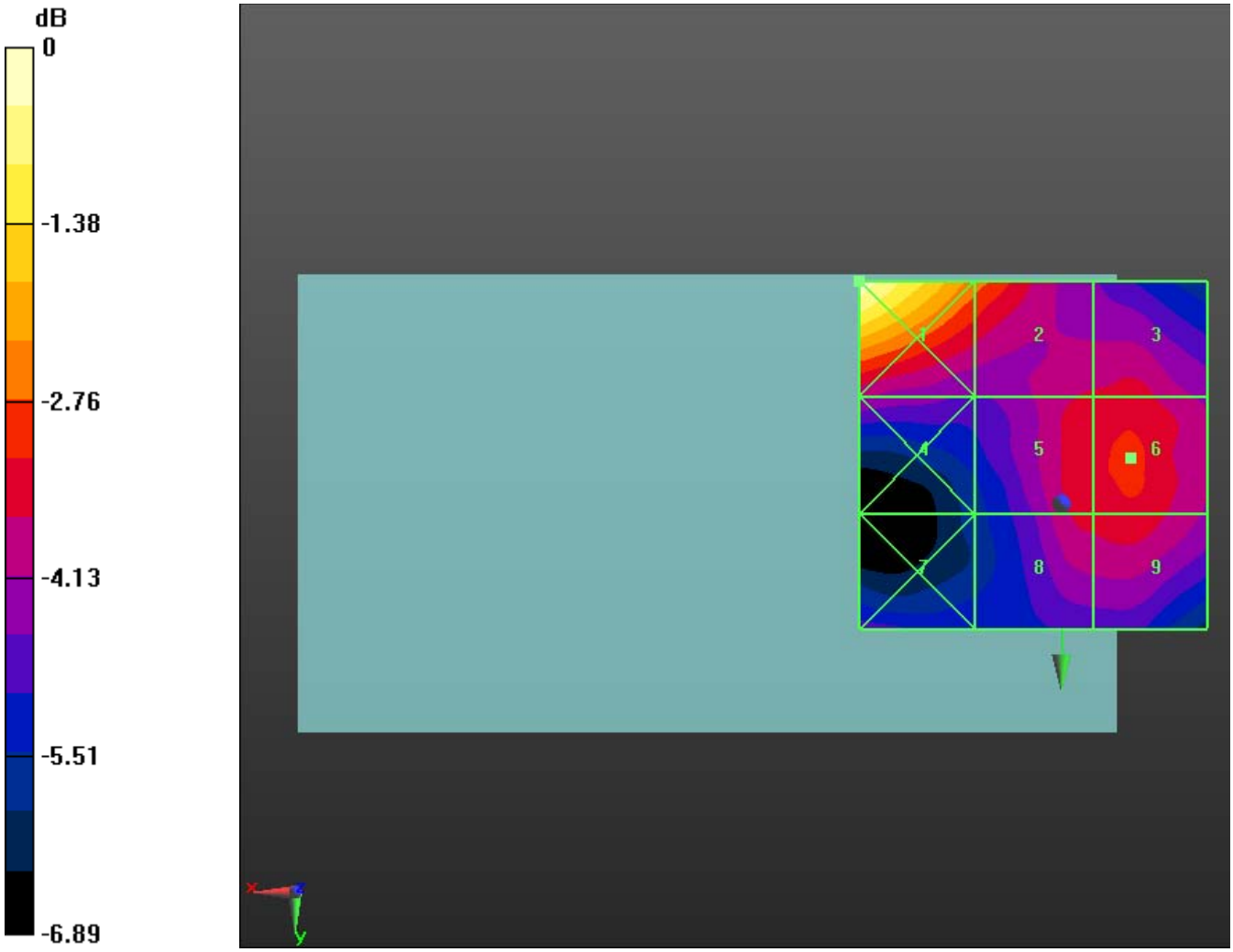
PMF scaled H-field

Grid 1 **M2** **0.27 A/m**	Grid 2 **M3** **0.20 A/m**	Grid 3 **M3** **0.18 A/m**
Grid 4 **M3** **0.17 A/m**	Grid 5 **M3** **0.18 A/m**	Grid 6 **M3** **0.19 A/m**
Grid 7 **M3**	Grid 8 **M3**	Grid 9 **M3**

0.16 A/m	**0.18 A/m**	**0.18 A/m**

Cursor:

Total = 0.266 A/m
H Category: M2
Location: 29, -32, 8.7 mm



0 dB = 0.270A/m = -11.37 dB A/m

Date/Time: 12/18/2012 7:14:18 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_UMTS_Band_II

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: WCDMA FDD II; Frequency: 1852.4 MHz, Frequency: 1880 MHz, Frequency: 1907.6 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field UMTS band II_measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_low_chan/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.08 V/m; Power Drift = -0.11 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.09 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.09 A/m**	Grid 2 **M4** **0.08 A/m**	Grid 3 **M4** **0.08 A/m**
Grid 4 **M4** **0.07 A/m**	Grid 5 **M4** **0.08 A/m**	Grid 6 **M4** **0.08 A/m**
Grid 7 **M4**	Grid 8 **M4**	Grid 9 **M4**

0.08 A/m	**0.07 A/m**	**0.07 A/m**

Cursor:
Total = 0.088 A/m
H Category: M4
Location: 25, -25, 8.7 mm

Device H-Field UMTS band II_measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_mid_chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.09 V/m; Power Drift = -0.01 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.09 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.09 A/m**	Grid 2 **M4** **0.08 A/m**	Grid 3 **M4** **0.08 A/m**
Grid 4 **M4** **0.07 A/m**	Grid 5 **M4** **0.08 A/m**	Grid 6 **M4** **0.08 A/m**
Grid 7 **M4** **0.09 A/m**	Grid 8 **M4** **0.08 A/m**	Grid 9 **M4** **0.08 A/m**

Cursor:
Total = 0.087 A/m
H Category: M4
Location: 25, -25, 8.7 mm

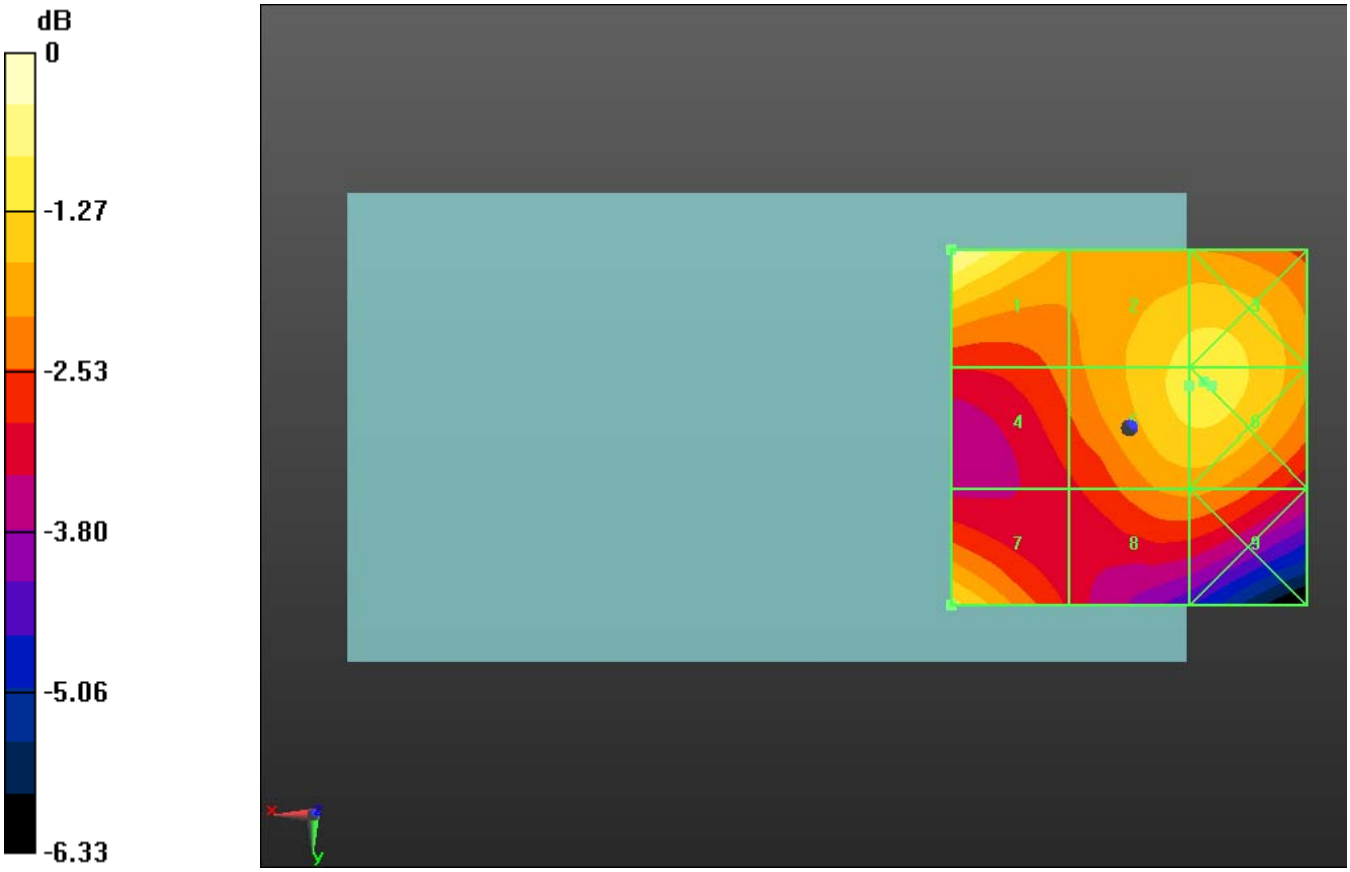
Device H-Field UMTS band II_measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_high_chan/Hearing Aid Compatibility Test (101x101x1):

Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.09 V/m; Power Drift = 0.04 dB
PMR not calibrated. PMF = 1.000 is applied.
H-field emissions = 0.09 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.09 A/m**	Grid 2 **M4** **0.09 A/m**	Grid 3 **M4** **0.09 A/m**
Grid 4 **M4** **0.07 A/m**	Grid 5 **M4** **0.09 A/m**	Grid 6 **M4** **0.09 A/m**
Grid 7 **M4** **0.09 A/m**	Grid 8 **M4** **0.08 A/m**	Grid 9 **M4** **0.08 A/m**

Cursor:
Total = 0.091 A/m
H Category: M4
Location: -11.5, -6, 8.7 mm



0 dB = 0.090A/m = -20.92 dB A/m

Date/Time: 12/18/2012 11:16:15 PM

Test Laboratory: RIM Testing Services

HAC RF_H-Field_GSM1900_Telecoil_2100_Battery

DUT: BlackBerry Smartphone; Type: Sample ; Serial: 25CF0BA5

Communication System: GSM 1900; Frequency: 1880 MHz
Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2007)

DASY Configuration:

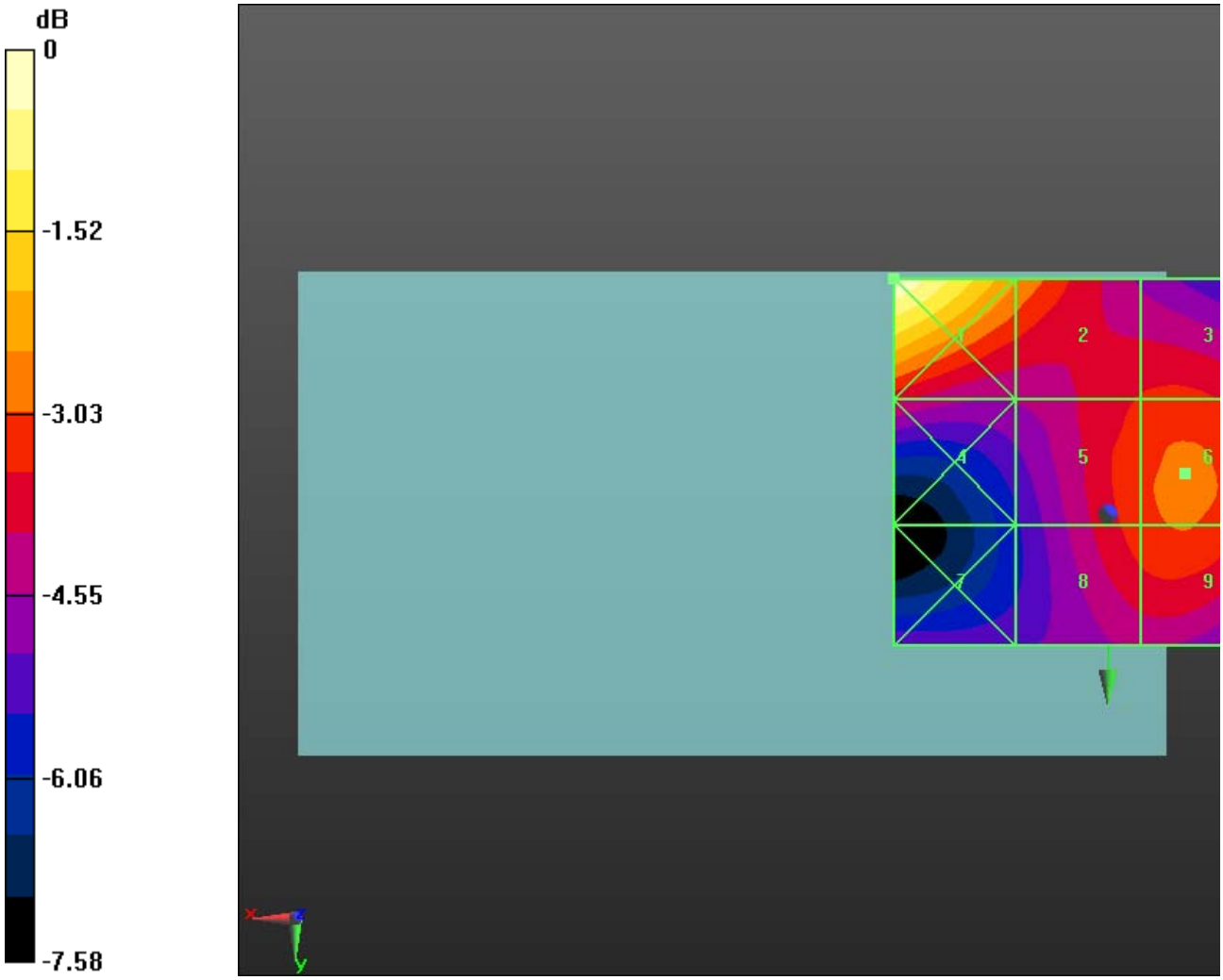
- Probe: H3DV6 - SN6105; ; Calibrated: 11/9/2012
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE3 Sn473; Calibrated: 1/13/2012
- Phantom: HAC RF Test Arch with AMCC; Type: SD HAC P01 BA
- DASY52 52.8.0(692); SEMCAD X 14.6.4(4989)

Device H-Field GSM 1900_measurement with H3DV6 probe/H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device_Centre_Telecoil_2100_Battery/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.07 V/m; Power Drift = -0.11 dB
PMR not calibrated. PMF = 2.860 is applied.
H-field emissions = 0.21 A/m
Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

Grid 1 **M2** **0.28 A/m**	Grid 2 **M3** **0.21 A/m**	Grid 3 **M3** **0.19 A/m**
Grid 4 **M3** **0.18 A/m**	Grid 5 **M3** **0.19 A/m**	Grid 6 **M3** **0.20 A/m**

Grid 7 **M3**	Grid 8 **M3**	Grid 9 **M3**
0.16 A/m	**0.19 A/m**	**0.20 A/m**



0 dB = 0.280A/m = -11.06 dB A/m